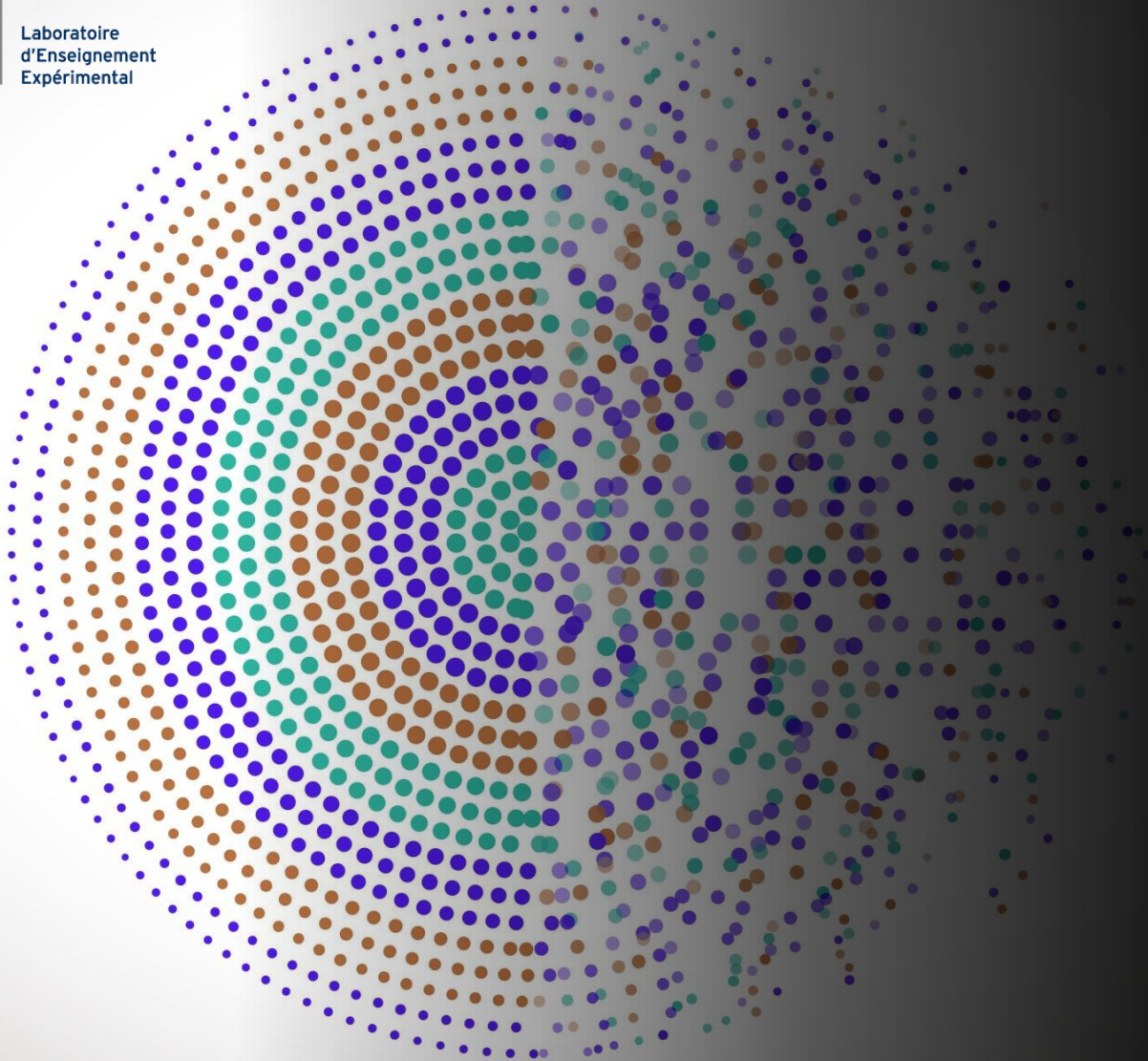


Bases de photodétection

Opto-Electronique / Semestre 5
Institut d'Optique

Julien VILLEMEJANE



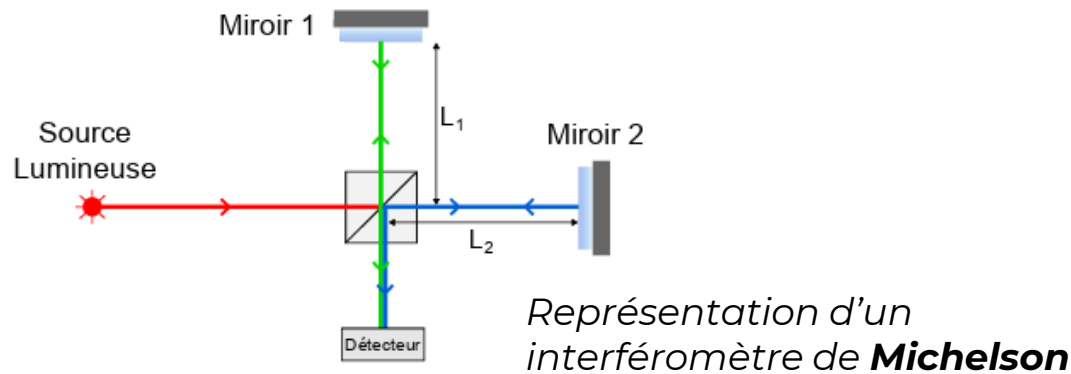
Photodétection

Exemples

Opto-Electronique / Semestre 5
Institut d'Optique

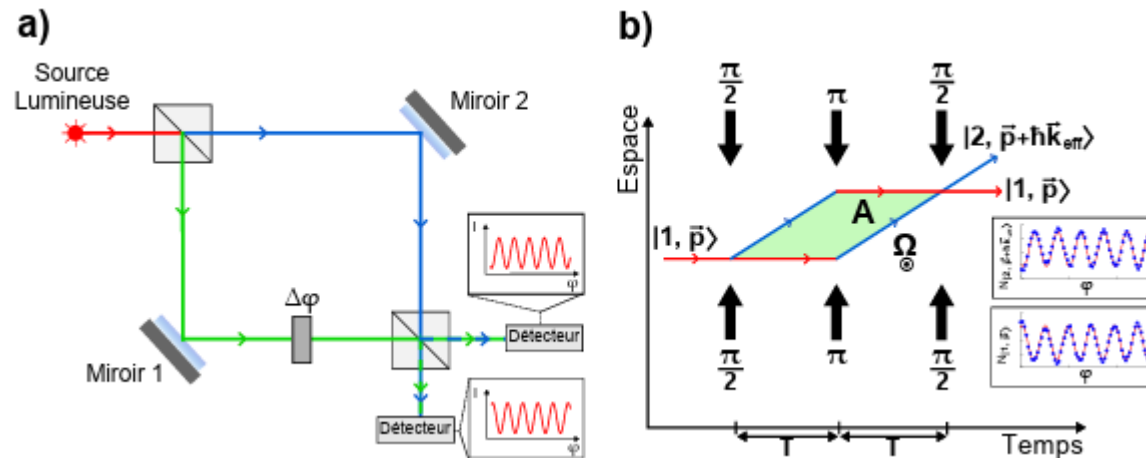
Julien VILLEMEJANE

Quelques utilisations des photodiodes



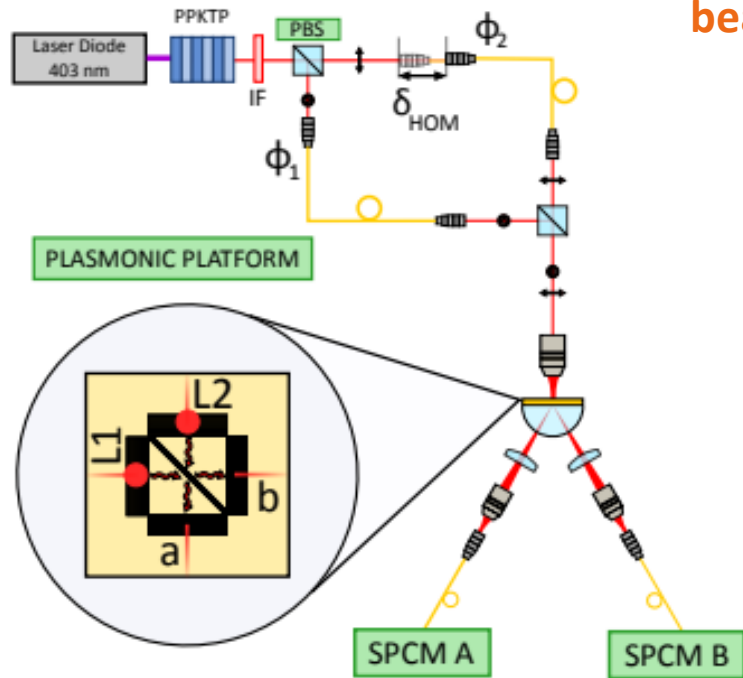
Interféromètre à atomes froids piégés sur puce avec séparation spatiale

Groupe Gaz Quantiques / LCF



Représentation d'un interféromètre de **Mach-Zehnder** (a) en optique, et (b) en version atomique, aussi appelé Ramsey-Bordé.

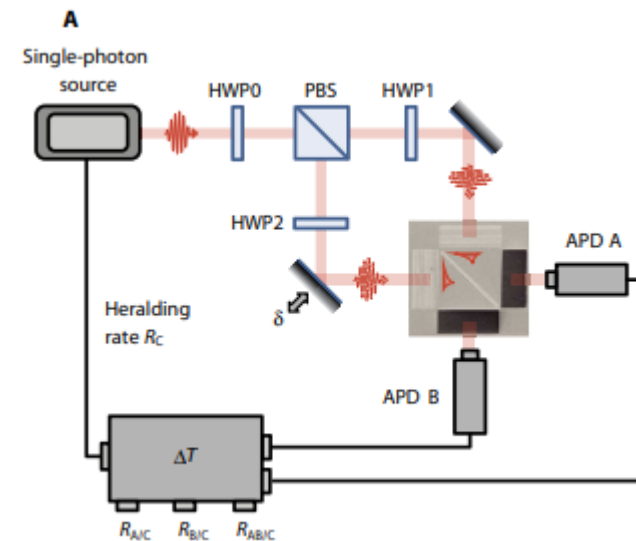
Quelques utilisations des photodiodes



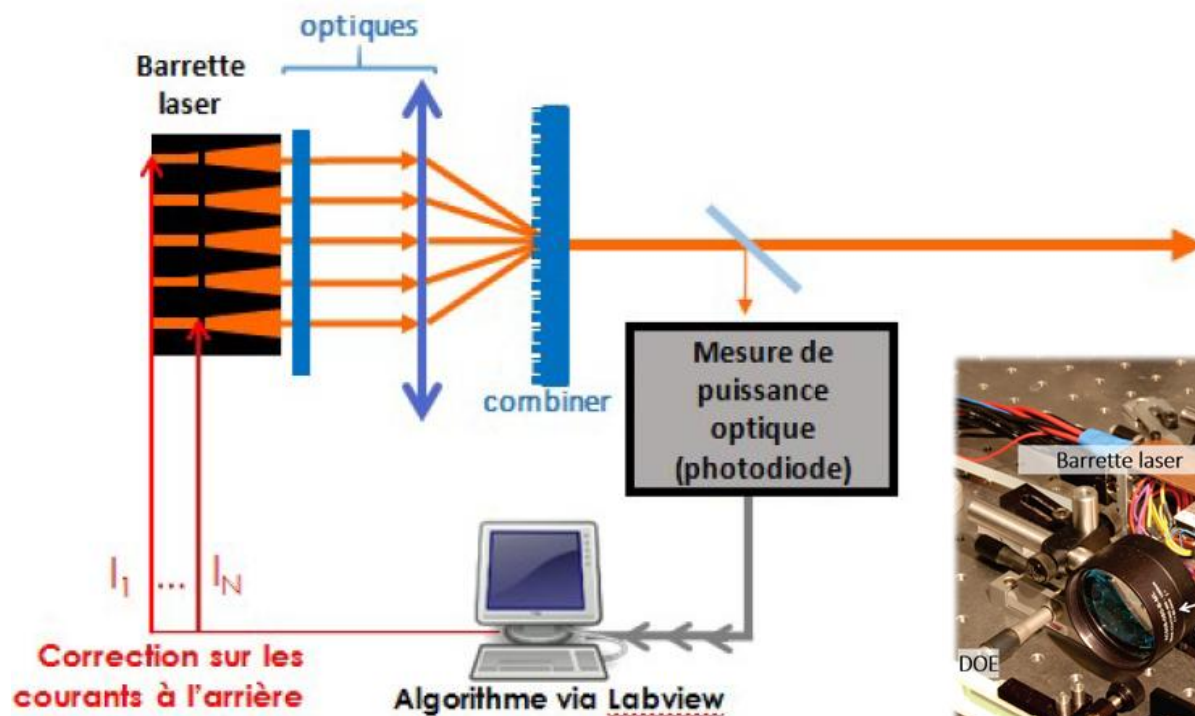
Anti-coalescence of bosons on a lossy beamsplitter

Groupe Nanophotonique / LCF

Single-plasmon interferences

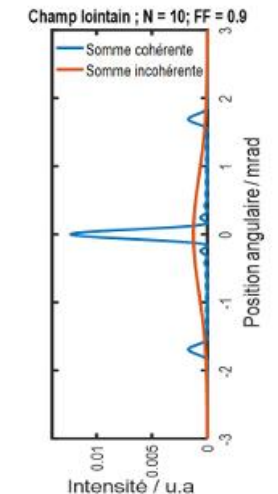
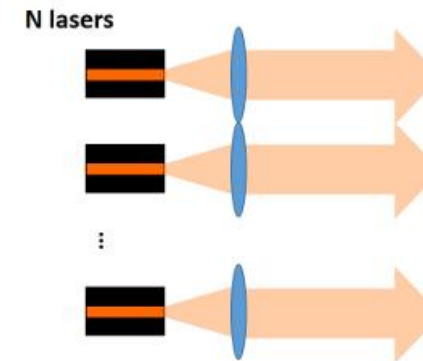
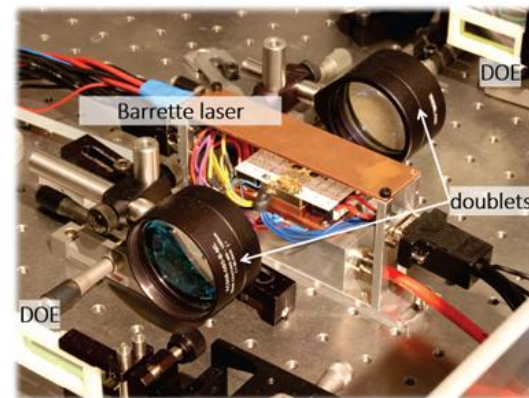


Quelques utilisations des photodiodes

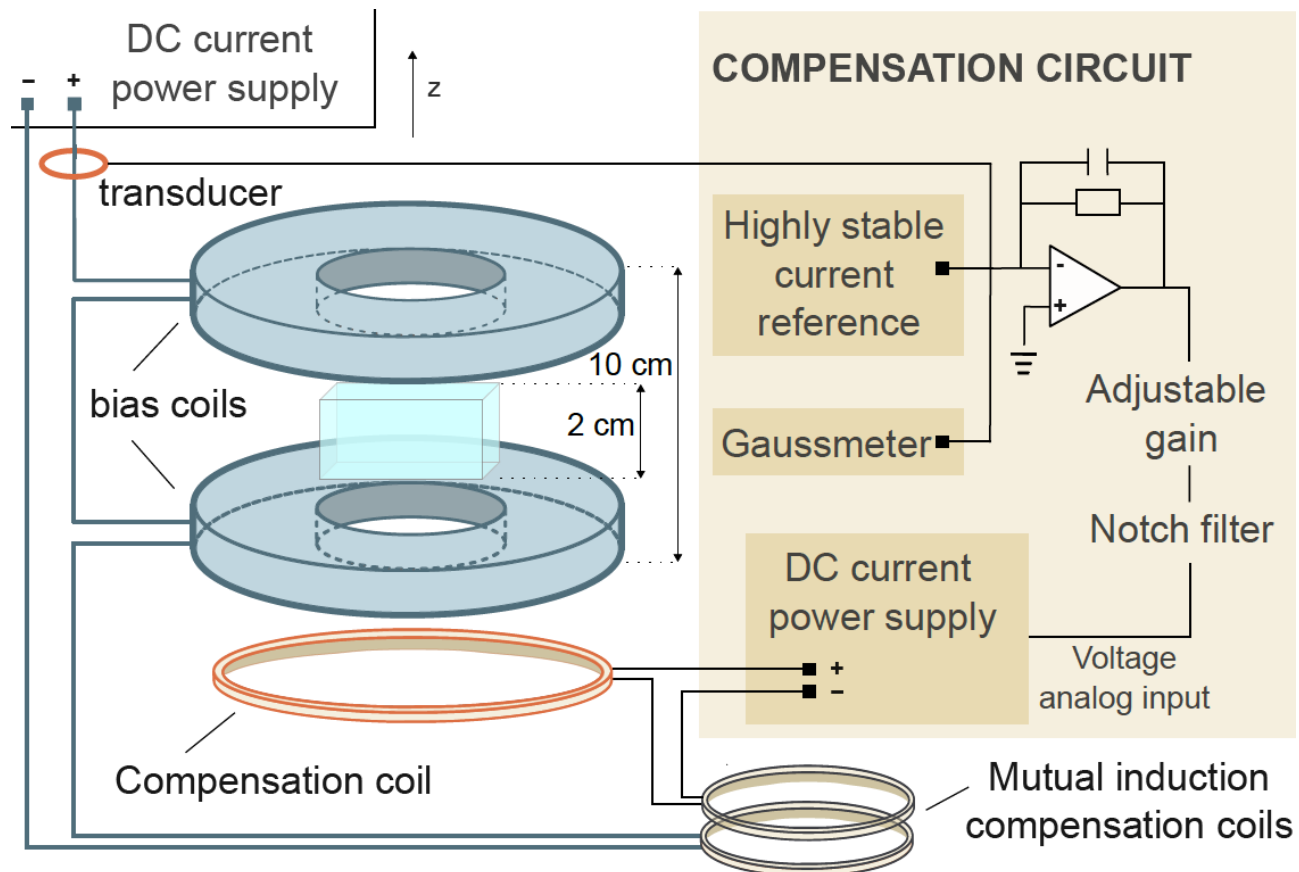


Combinaison cohérente de diodes laser de puissance

Groupe Laser / LCF



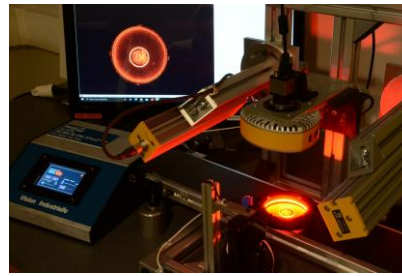
Quelques utilisations des photodiodes



Magnetic field stabilisation for Bose-Einstein condensation experiments

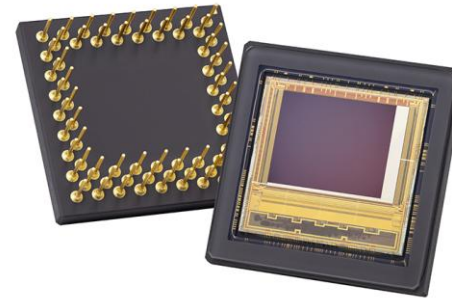
Groupe Gaz Quantique / LCF

Schematic of the **stabilization system**. In essence, it is a **feedforward** technique in a separated coil. A key feature is that the mutual inductance between the two circuits is cancelled.



SC19 – Cameras and Interfaces

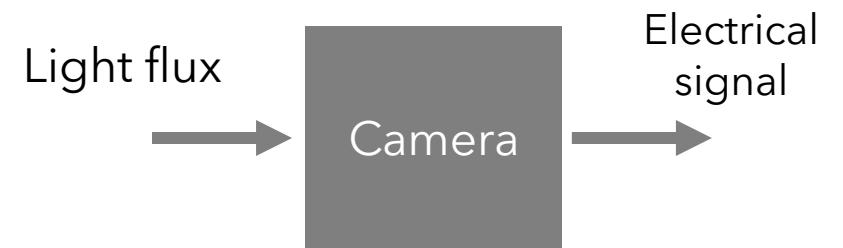
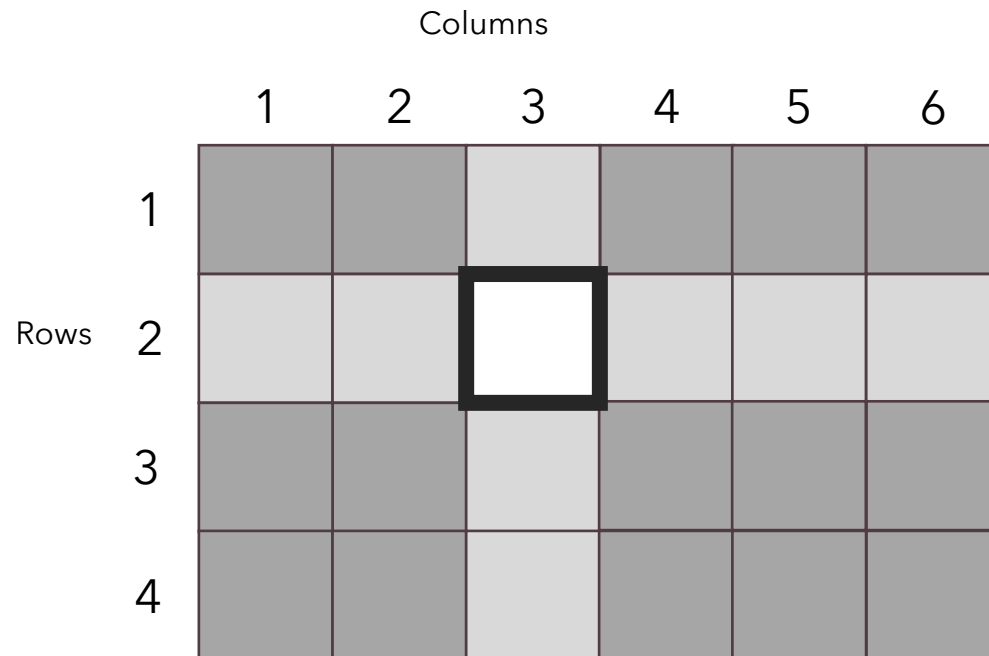
Camera / Array of small sensors

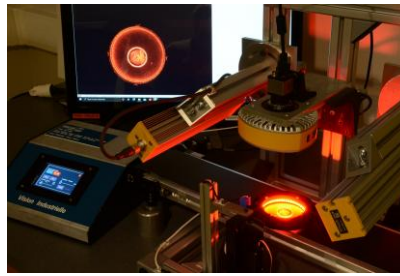


<https://imaging.teledyne-e2v.com/products/2d-cmos-image-sensors/onyxmax/>

Camera

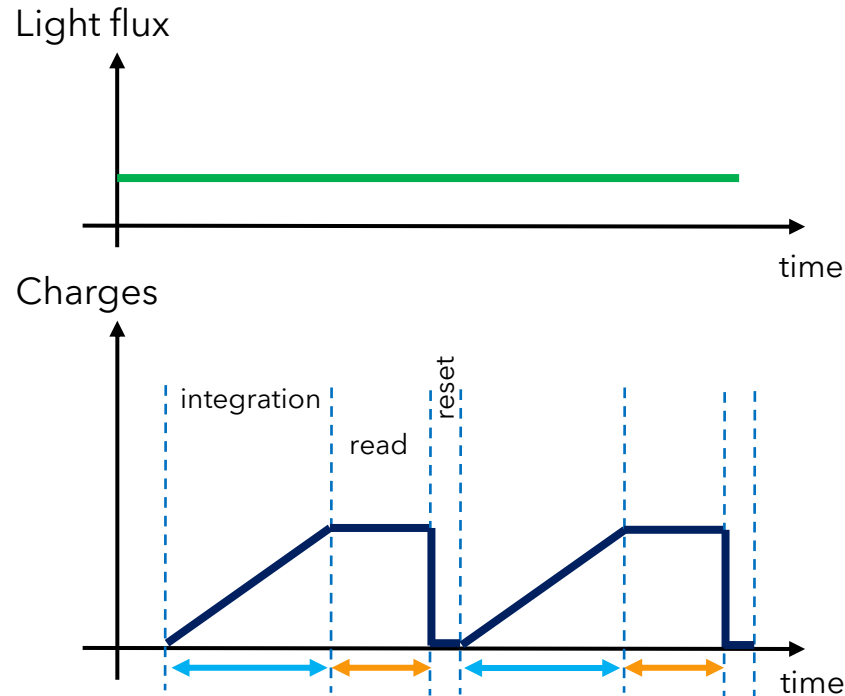
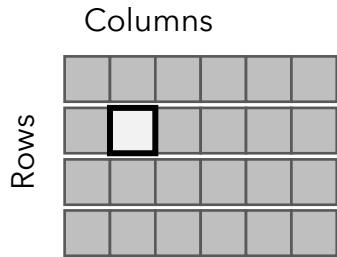
Device that transforms a **light flux** into a **measurable electrical signal**





SC19 – Cameras and Interfaces

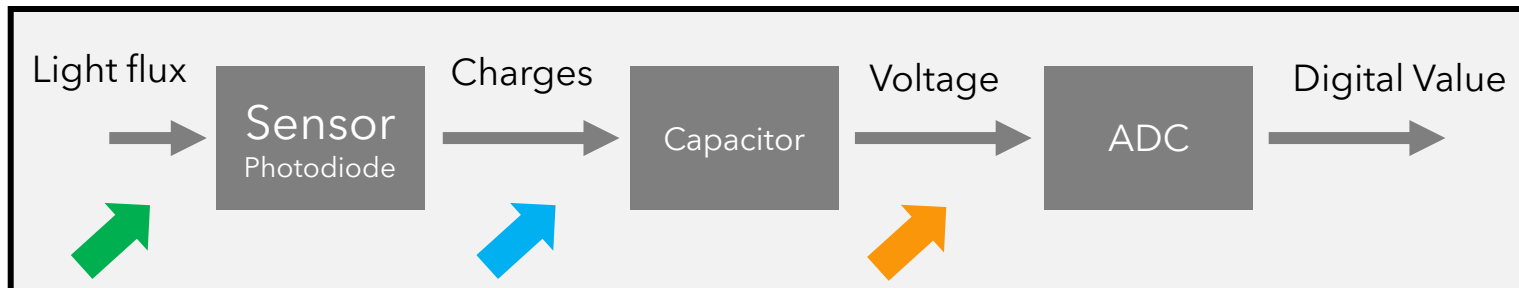
Exposure Time

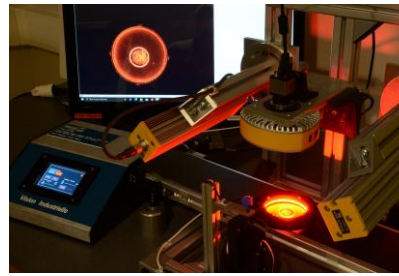


Exposure Time

Duration for which the **camera's sensor is exposed to light**, when capturing an image.

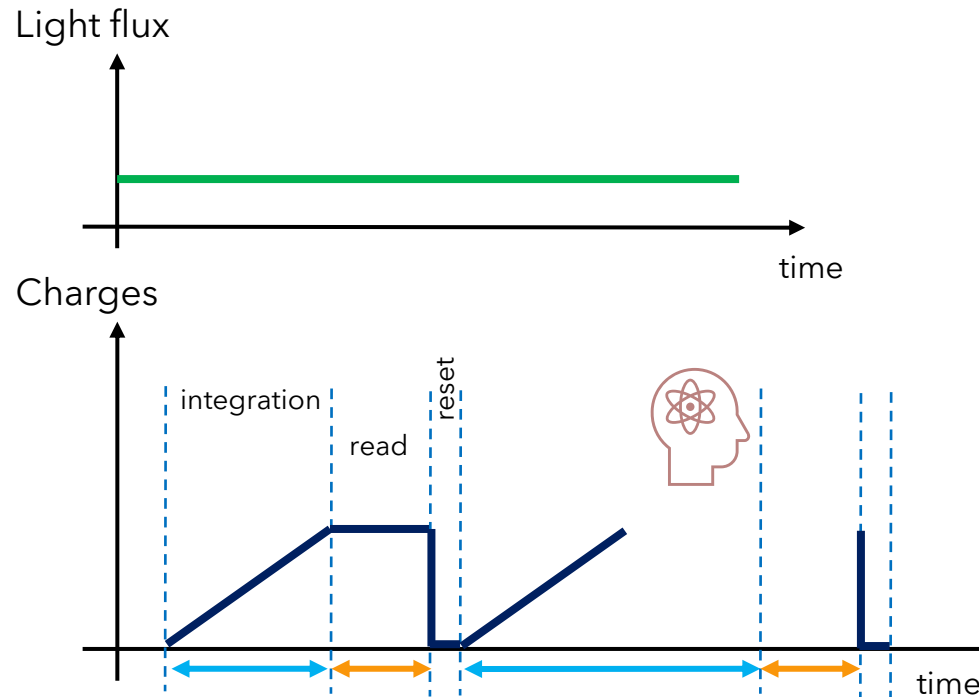
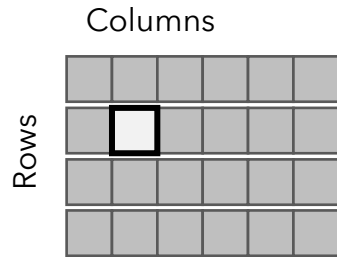
This parameter determines the amount of light collected. i.e. the amount of collected charges coming from the sensor stored in a capacitor





SC19 – Cameras and Interfaces

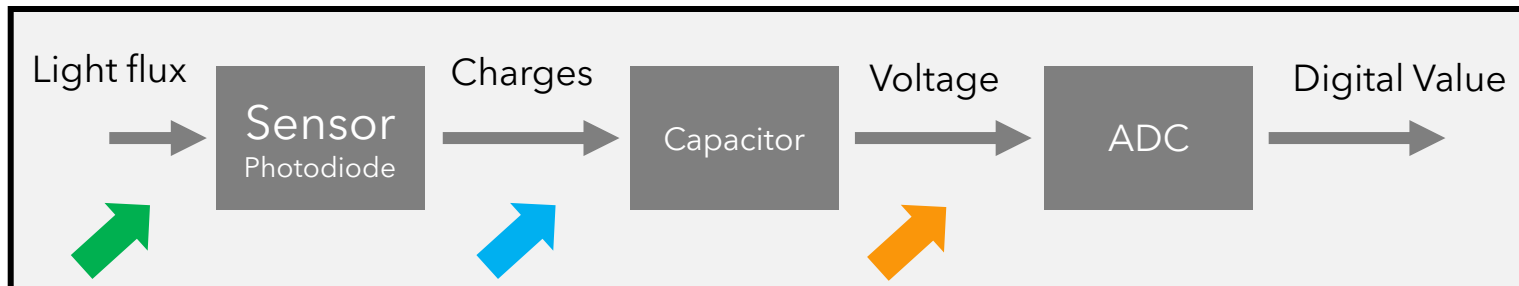
Exposure Time

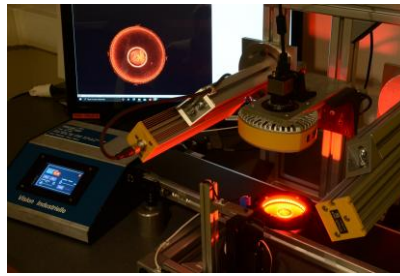


Exposure Time

Duration for which the **camera's sensor is exposed to light**, when capturing an image.

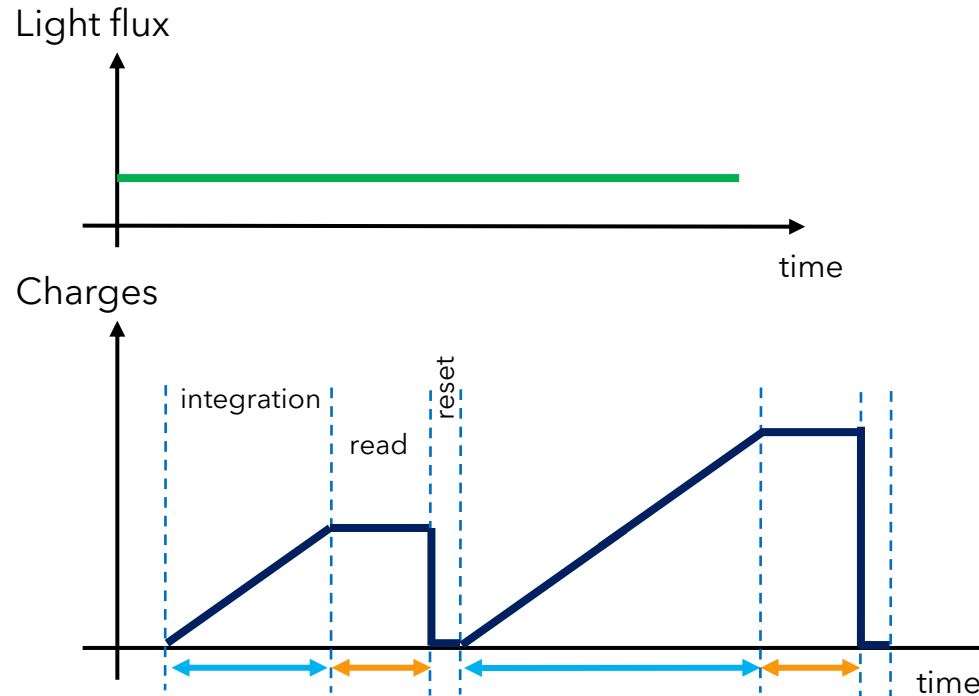
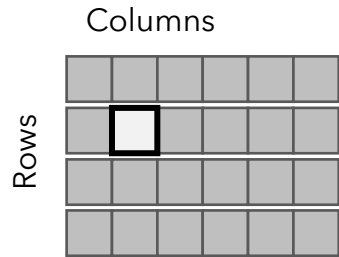
This parameter determines the amount of light collected. i.e. the amount of collected charges coming from the sensor stored in a capacitor





SC19 – Cameras and Interfaces

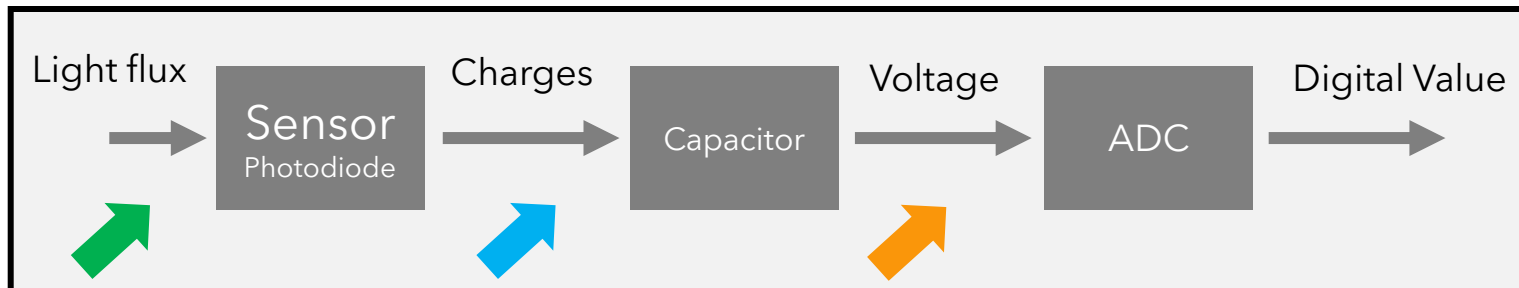
Exposure Time

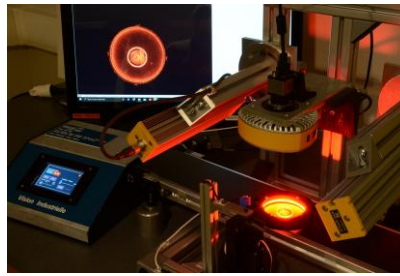


Exposure Time

Duration for which the **camera's sensor is exposed to light**, when capturing an image.

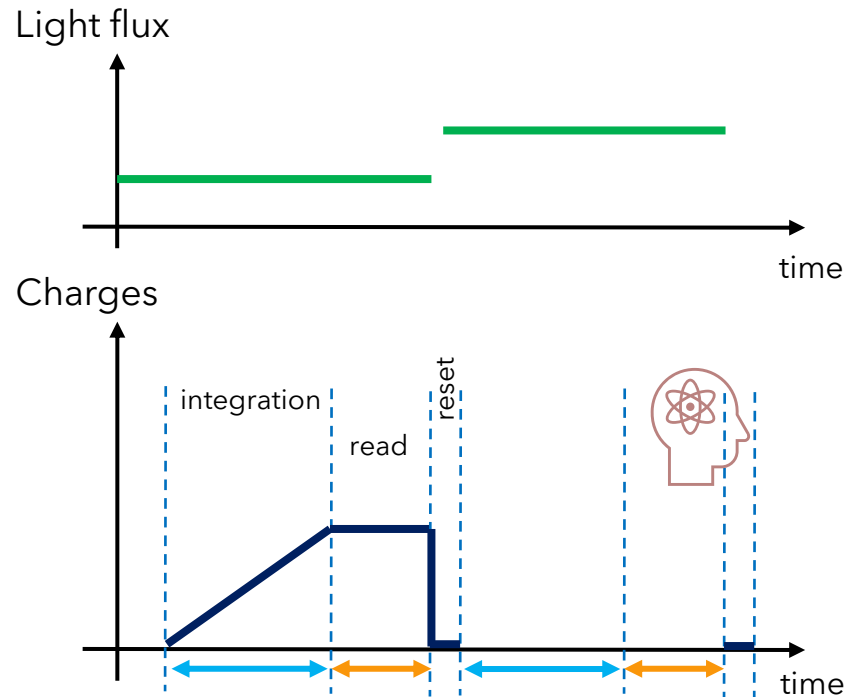
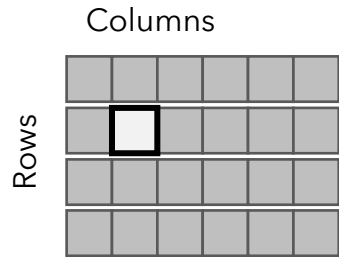
This parameter determines the amount of light collected. i.e. the amount of collected charges coming from the sensor stored in a capacitor





SC19 – Cameras and Interfaces

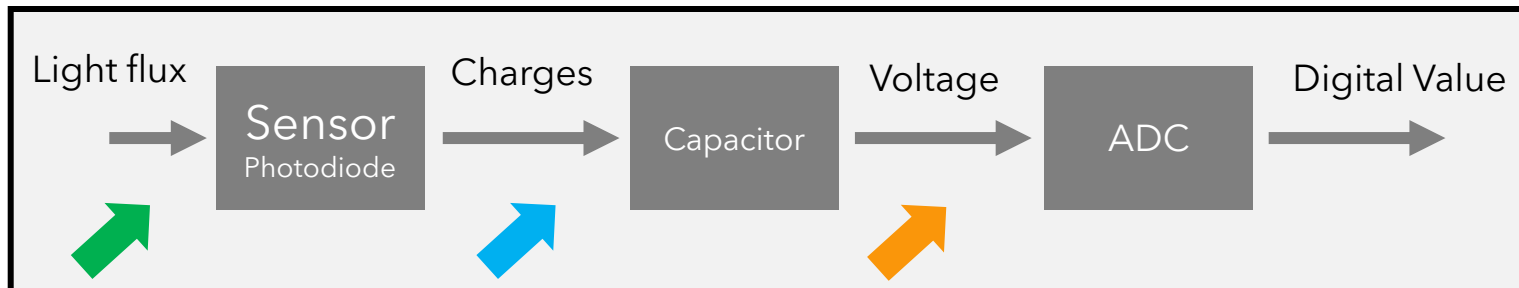
Exposure Time

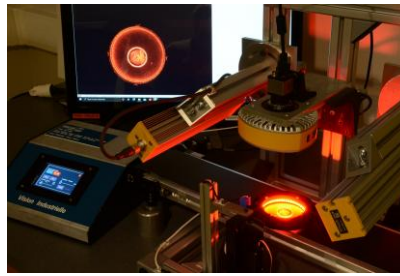


Exposure Time

Duration for which the **camera's sensor is exposed to light**, when capturing an image.

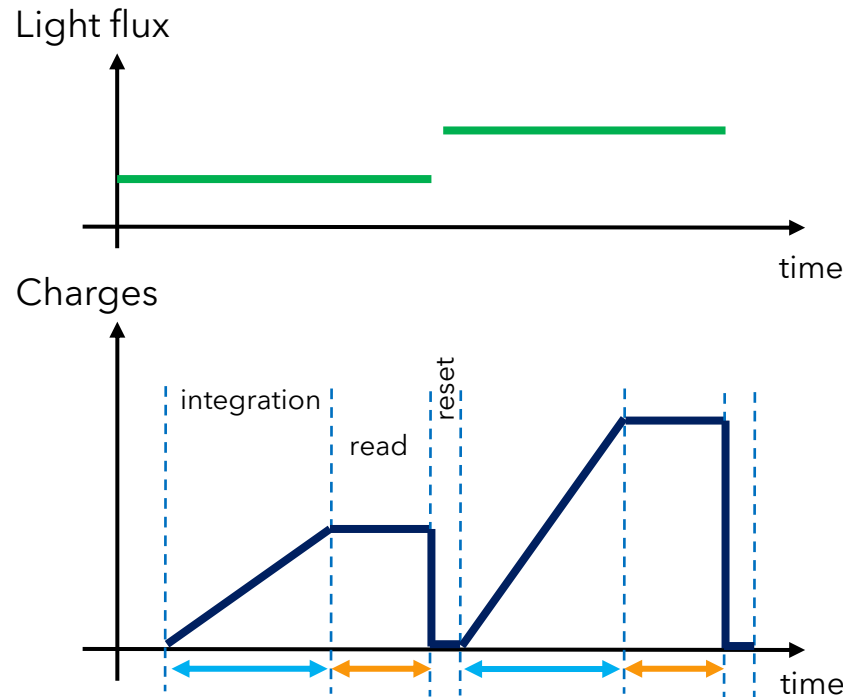
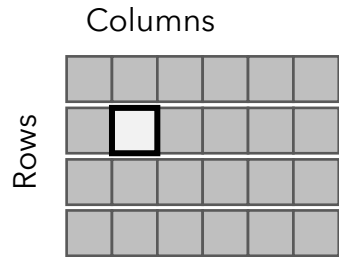
This parameter determines the amount of light collected. i.e. the amount of collected charges coming from the sensor stored in a capacitor





SC19 – Cameras and Interfaces

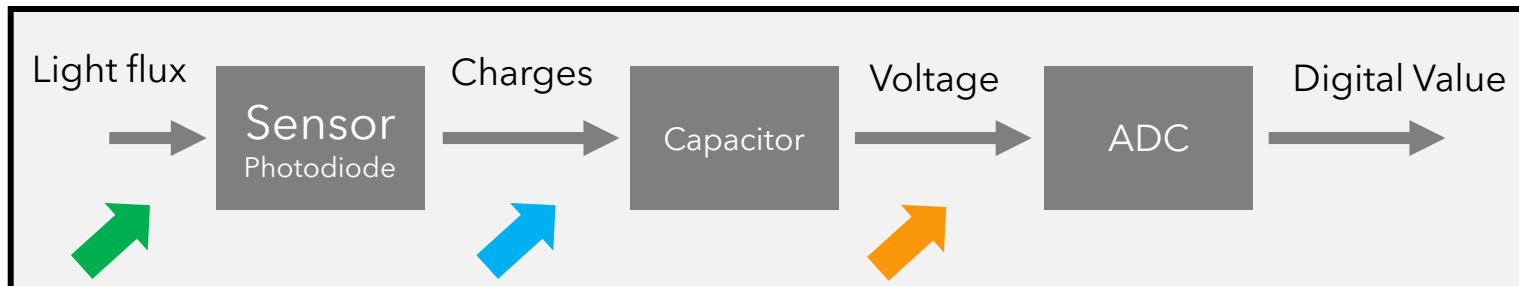
Exposure Time

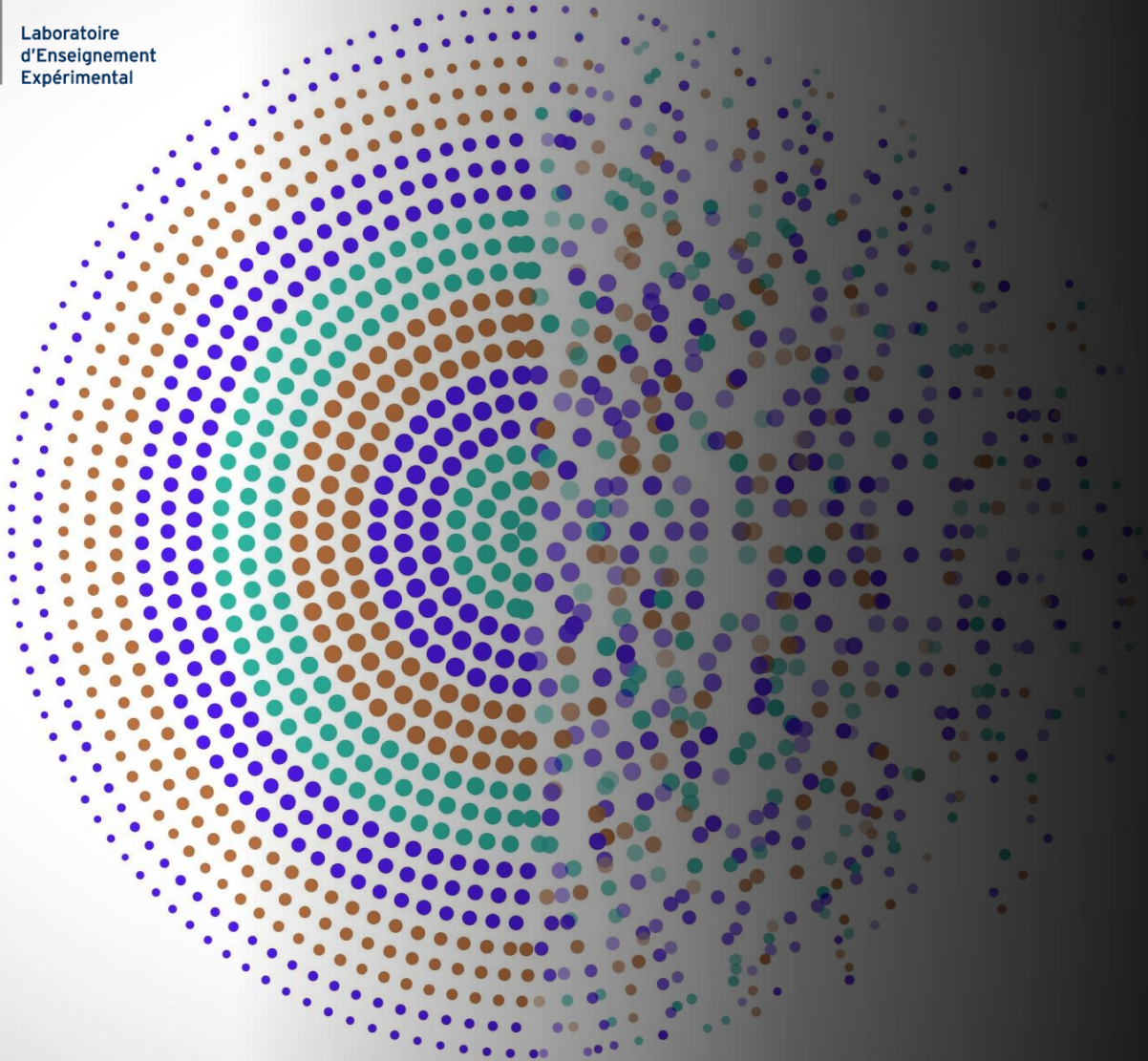


Exposure Time

Duration for which the **camera's sensor is exposed to light**, when capturing an image.

This parameter determines the amount of light collected. i.e. the amount of collected charges coming from the sensor stored in a capacitor



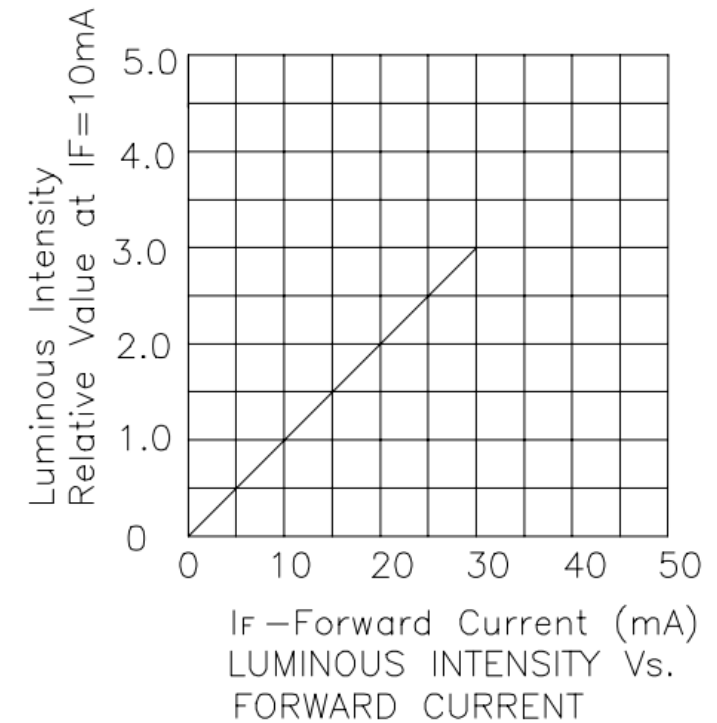
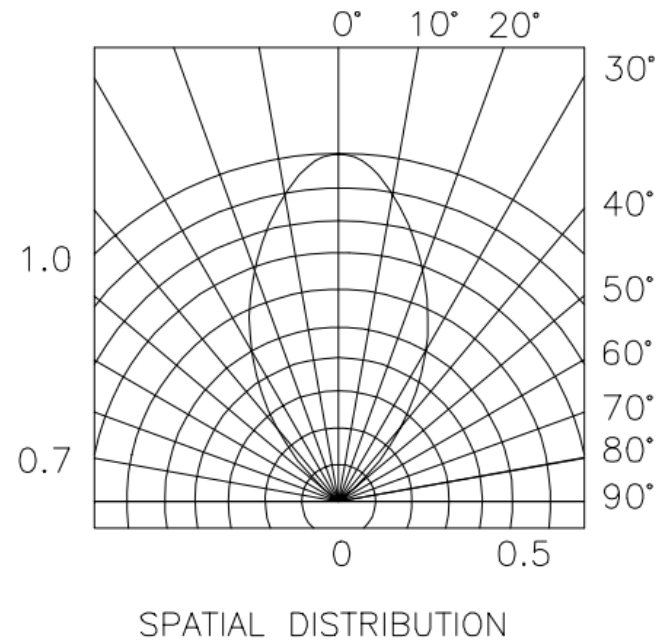
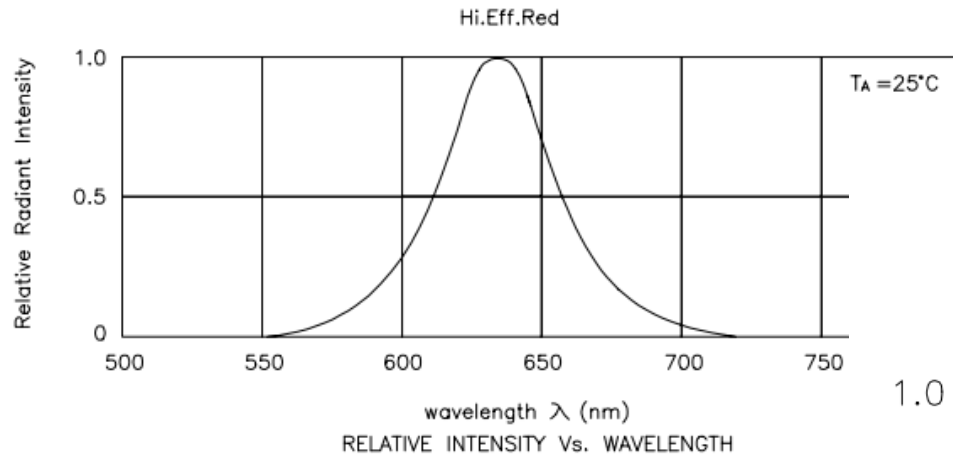


LEDs

Opto-Electronique / Semestre 5
Institut d'Optique

Julien VILLEMEJANE

LEDs et circuits d'émission



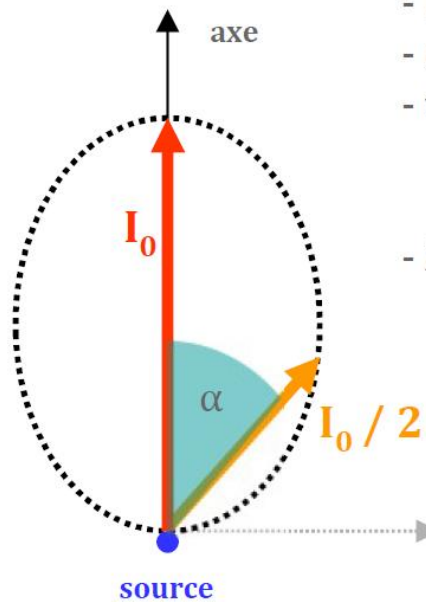
Source de photons

LEDs et circuits d'émission



Source de photons

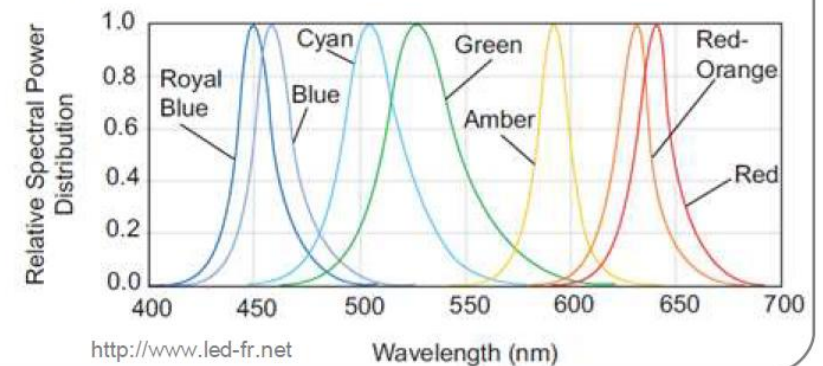
CARACTÉRISTIQUES OPTIQUES



- I_0 : intensité lumineuse sur l'axe
- α : demi-angle (directivité)
- η : rendement de conversion

$$\eta = \frac{\text{Nb photons émis}}{\text{Nb électrons}}$$

- λ : longueur d'onde d'émission

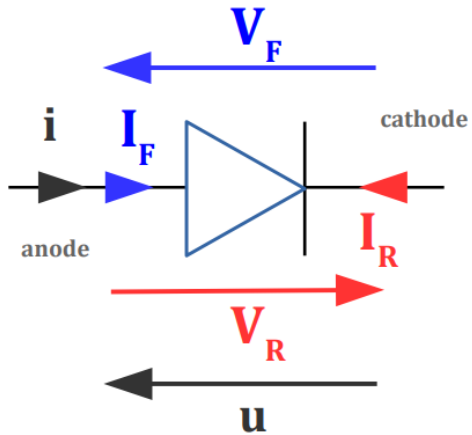


<http://www.led-fr.net>

Caractéristiques électriques d'une LED



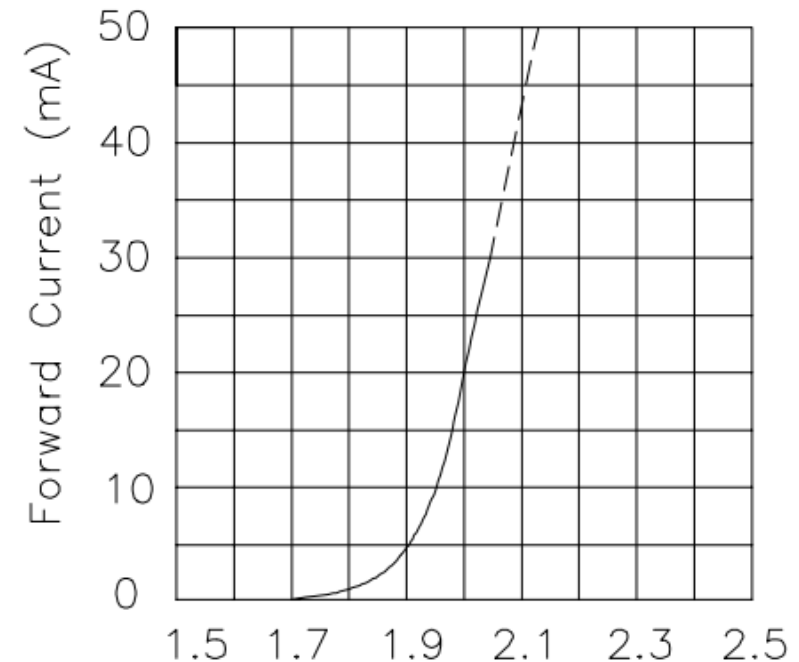
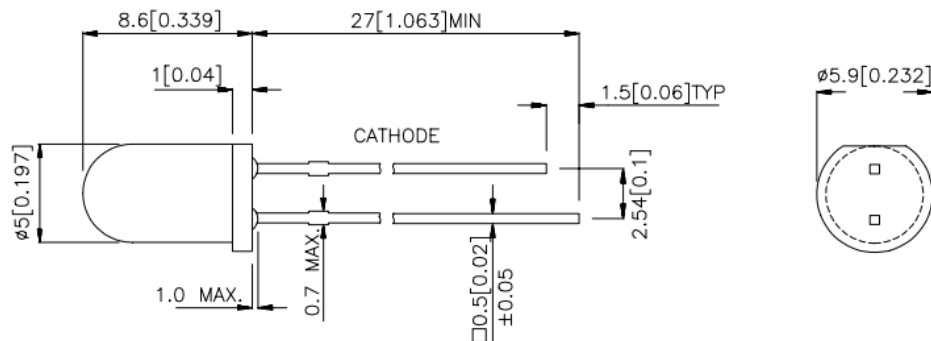
DIODE



I_F : **courant direct**
souvent $I_F < I_{FMAX}$

V_F : **tension directe**
aussi appelée seuil

I_R : **courant inverse**
 V_R : **tension inverse**
souvent $V_R < V_{RMAX}$



Forward Voltage(V)
FORWARD CURRENT Vs.
FORWARD VOLTAGE

Kingbright

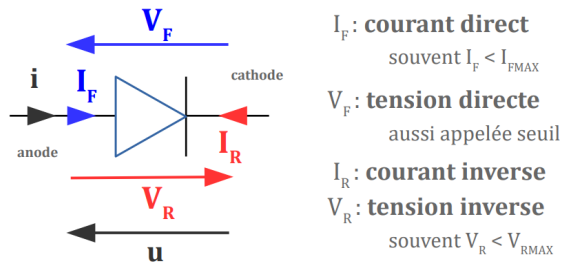
High Efficiency Red

L-531D

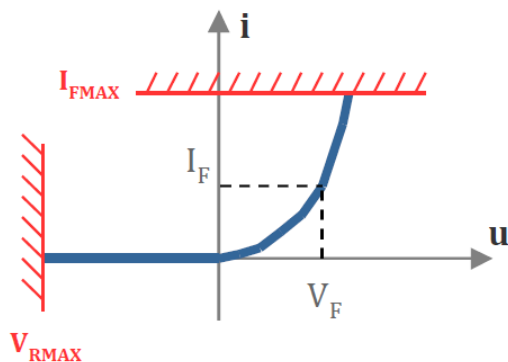
Caractéristiques électriques d'une LED



DIODE



MODÈLE COMPLET



$$e = -1,602 \times 10^{-19} \text{ C}$$

$$k = 1,38064852 \cdot 10^{-23} \text{ J/K}$$

Si $u > 0$, diode **passante**

$$i = I_0 [\exp(u / n.V_0) - 1]$$

loi exponentielle

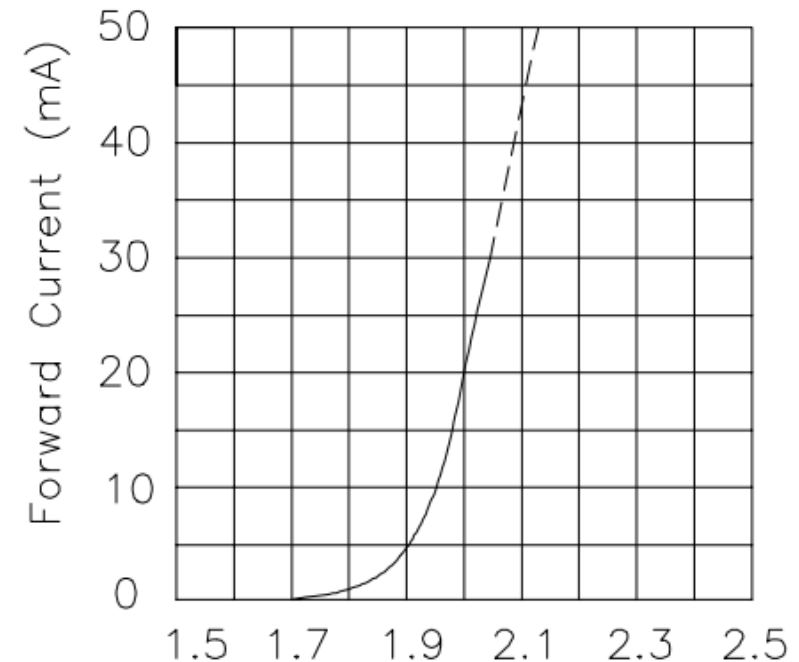
V_0 : tension thermique

$$V_0 = k.T / e$$

T : température (K)
 k : Constante de Boltzmann
 e : charge d'un électron

n : facteur de qualité

I_0 : constante spécifique à un type



Forward Voltage(V)
 FORWARD CURRENT Vs.
 FORWARD VOLTAGE

Kingbright

High Efficiency Red

L-53ID

Caractéristiques électriques d'une LED



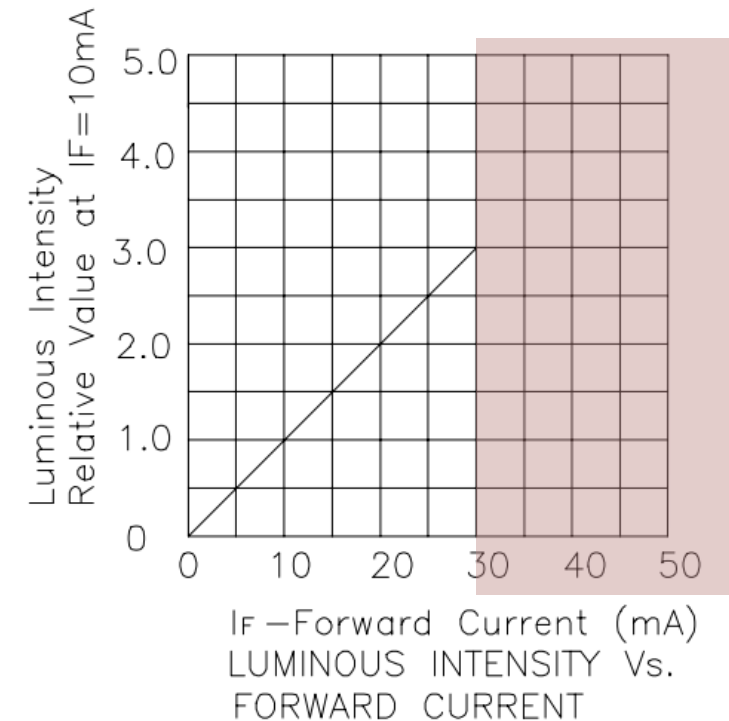
Idéalement : source de courant

Absolute Maximum Ratings at $T_A=25^\circ\text{C}$

Parameter	High Efficiency Red	Units
Power dissipation	105	mW
DC Forward Current	30	mA
Peak Forward Current [1]	160	mA
Reverse Voltage	5	V
Operating/Storage Temperature	-40°C To $+85^\circ\text{C}$	
Lead Solder Temperature [2]	260 $^\circ\text{C}$ For 5 Seconds	

Notes:

1. 1/10 Duty Cycle, 0.1ms Pulse Width.
2. 2mm below package base.



Kingbright

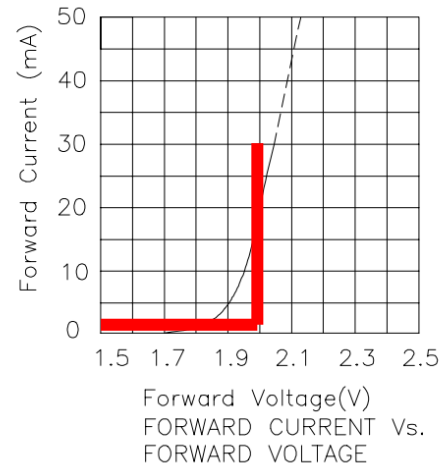
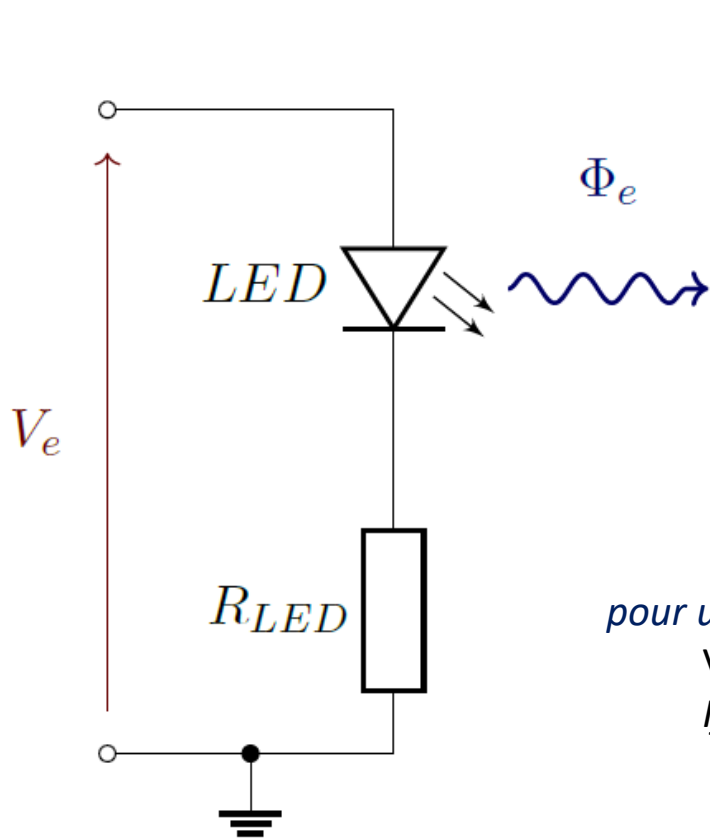
High Efficiency Red

L-53ID

Caractéristiques électriques d'une LED



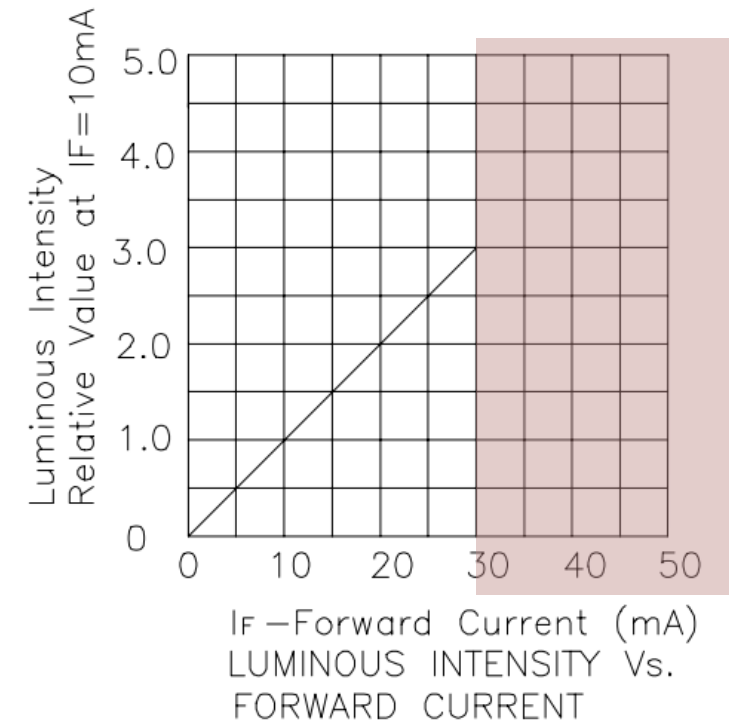
Idéalement : source de courant



pour une LED Rouge Standard

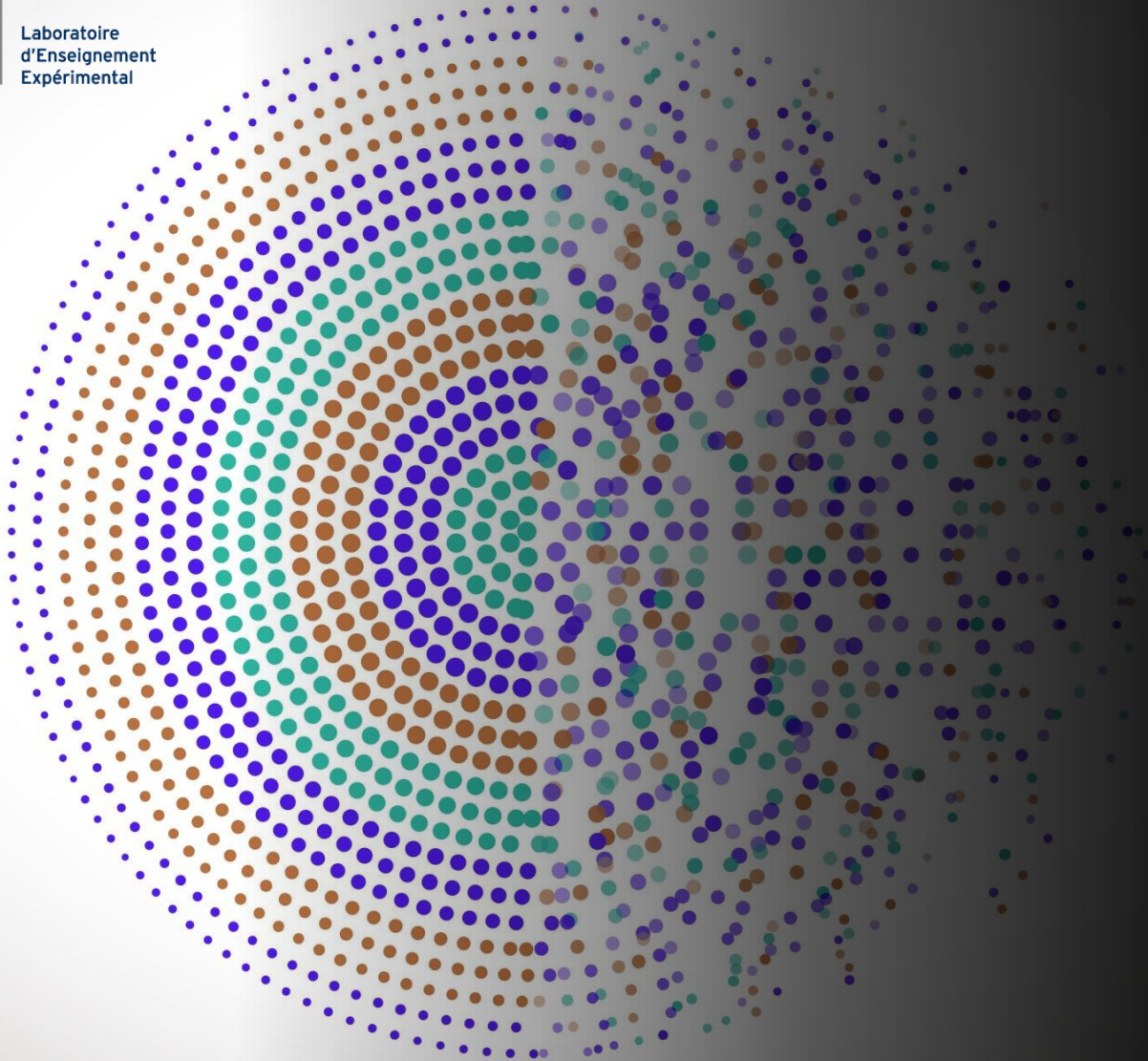
$$V_f = 2V$$

$$I_{f_{MAX}} = 30 \text{ mA}$$



High Efficiency Red

L-53ID

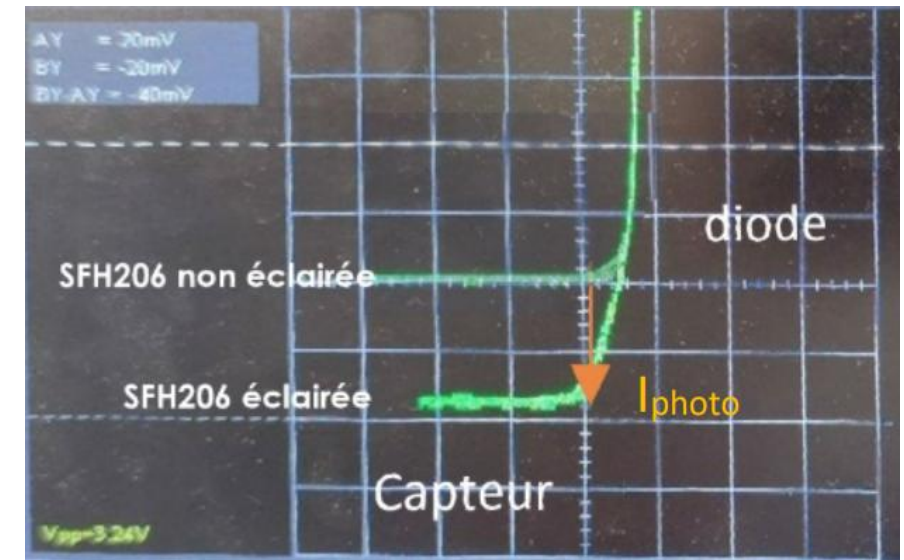
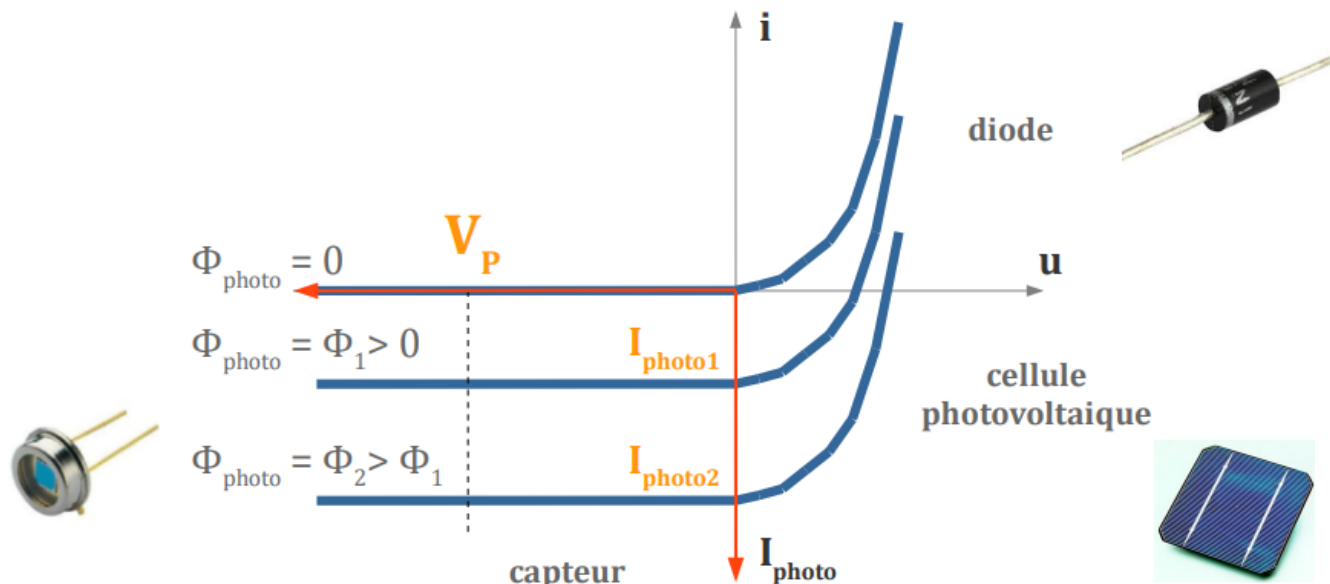
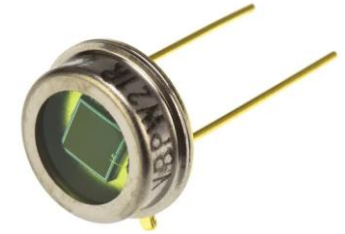


Photodétection

Opto-Electronique / Semestre 5
Institut d'Optique

Julien VILLEMEJANE

Photodiode, une diode mais...



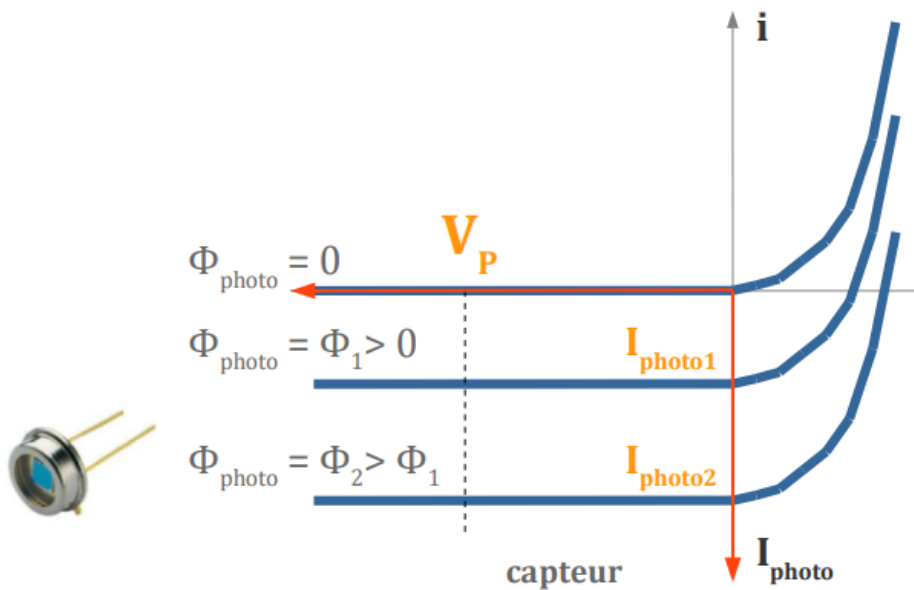
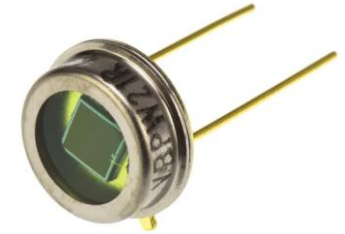
$$I_{\text{photo}} = S_{\lambda} \cdot \eta \cdot \Phi_{\text{photo}}$$

S_{λ} : Sensibilité spectrale
 η : Rendement quantique
 Φ_{photo} : Flux lumineux

<https://www.youtube.com/watch?v=KgKcbW77txY>

<https://www.youtube.com/watch?v=rNoHLOumplk>

Photodiode, une diode mais...

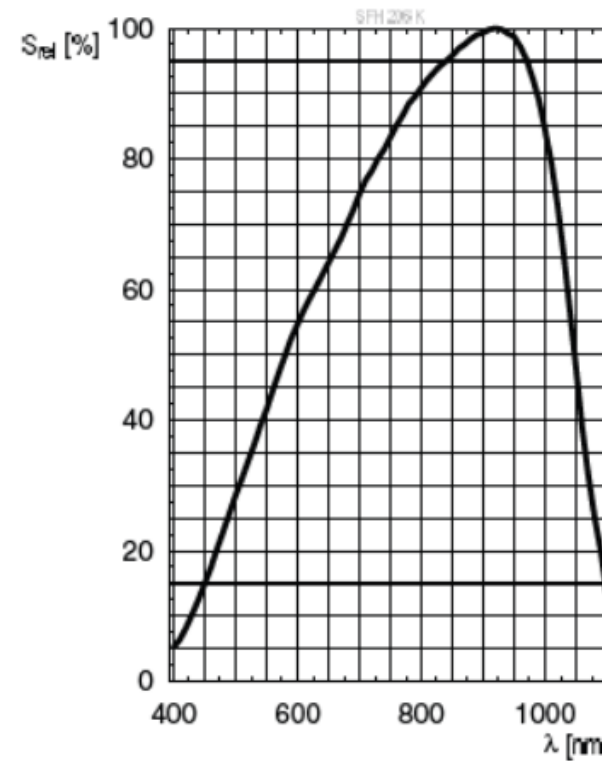


$$I_{\text{photo}} = S_{\lambda} \cdot \eta \cdot \Phi_{\text{photo}}$$

S_{λ} : Sensibilité spectrale
 η : Rendement quantique
 Φ_{photo} : Flux lumineux

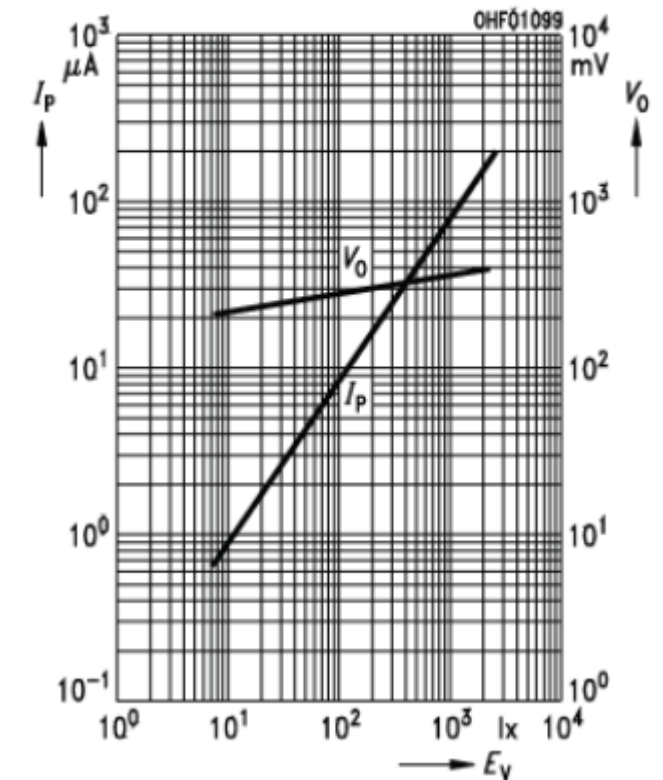
SFH 206 K

Relative Spectral Sensitivity

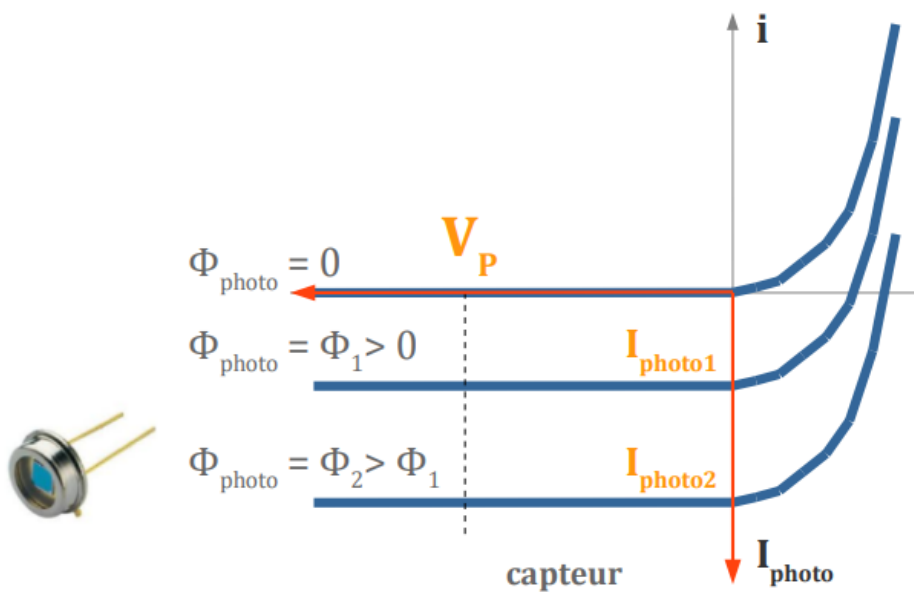
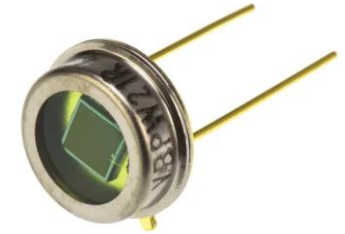


Photocurrent/Open-Circuit Voltage

$$I_P (V_R = 5 \text{ V}) / V_O = f(E_V)$$



Photodiode, une diode mais...

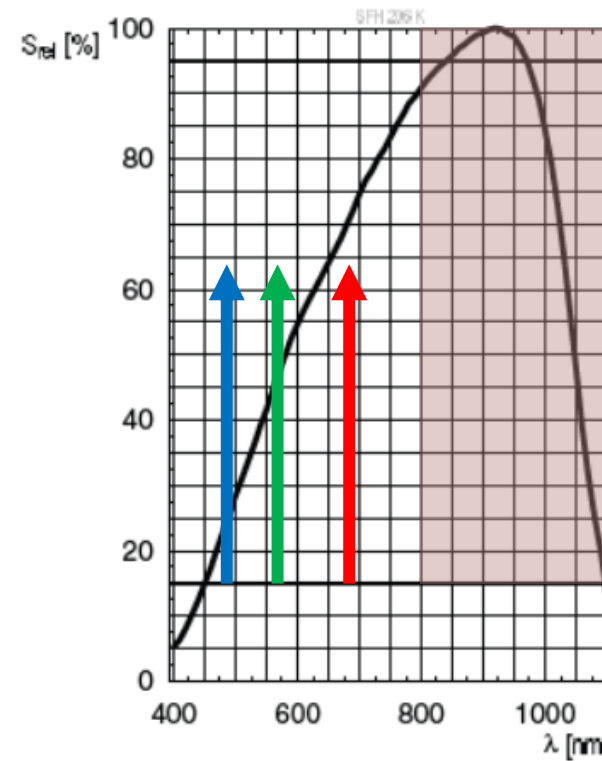


$$I_{\text{photo}} = S_{\lambda} \cdot \eta \cdot \Phi_{\text{photo}}$$

S_{λ} : Sensibilité spectrale
 η : Rendement quantique
 Φ_{photo} : Flux lumineux

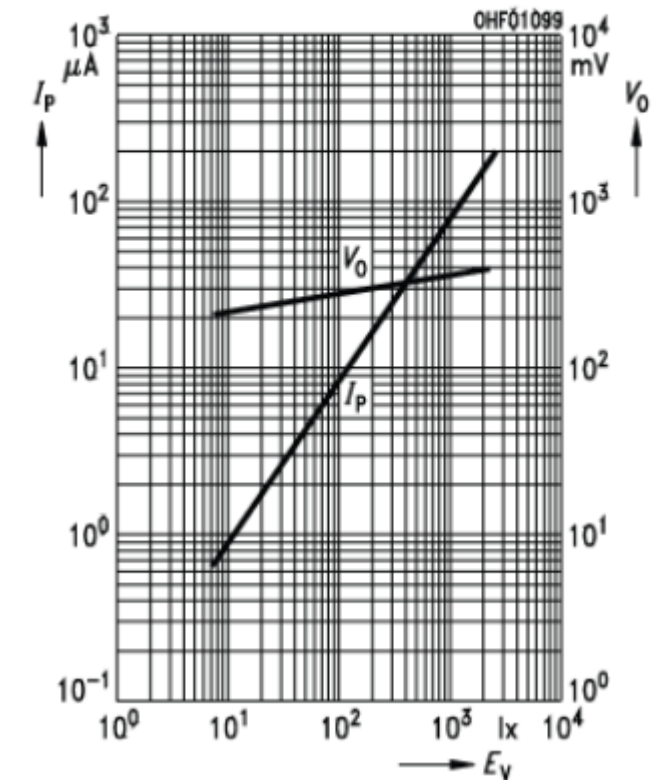
SFH 206 K

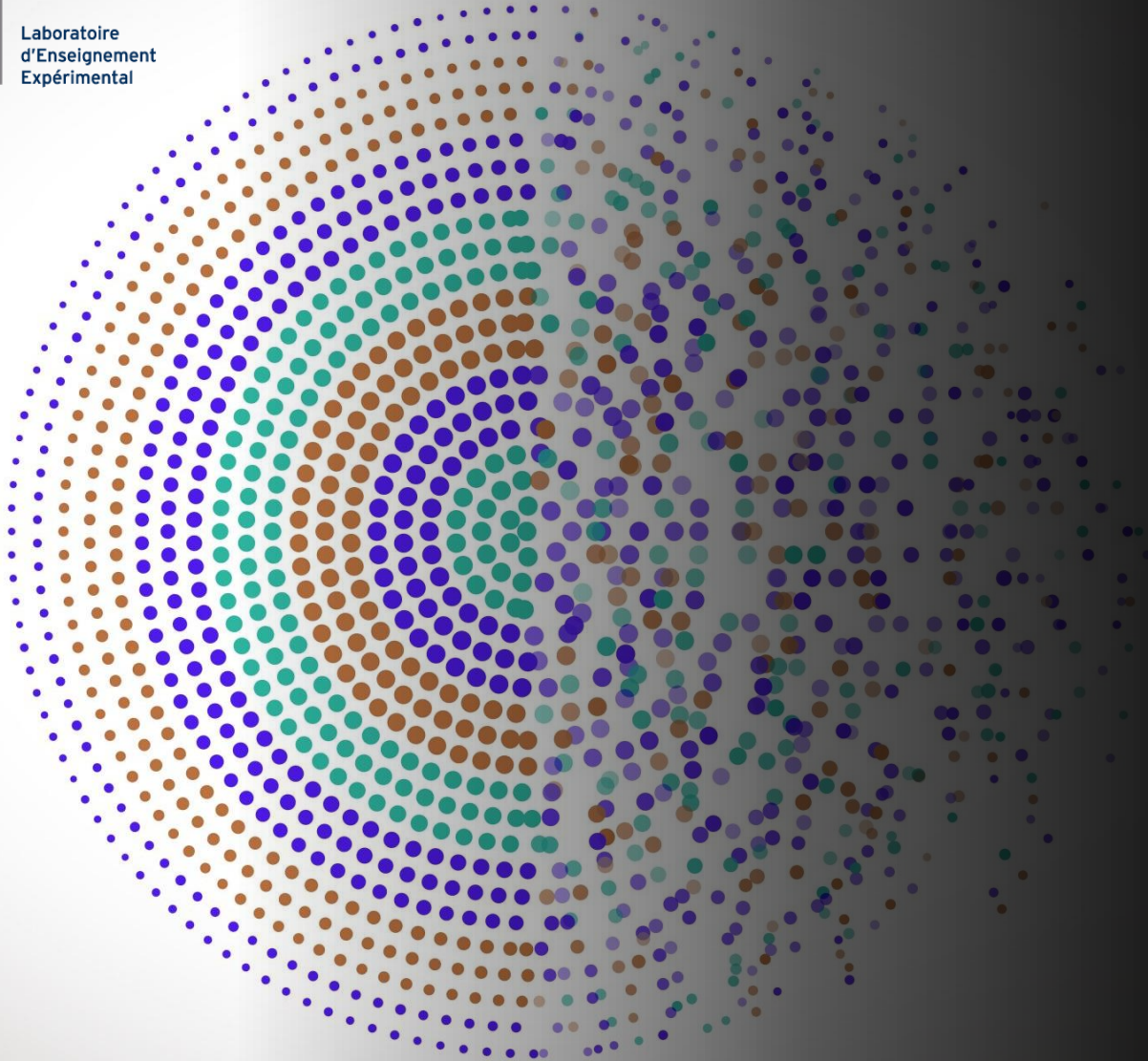
Relative Spectral Sensitivity



Photocurrent/Open-Circuit Voltage

$$I_P (V_R = 5 \text{ V}) / V_O = f(E_V)$$





Photodétection

Montage simple

Opto-Electronique / Semestre 5
Institut d'Optique

Julien VILLEMEJANE

Montage de photodétection

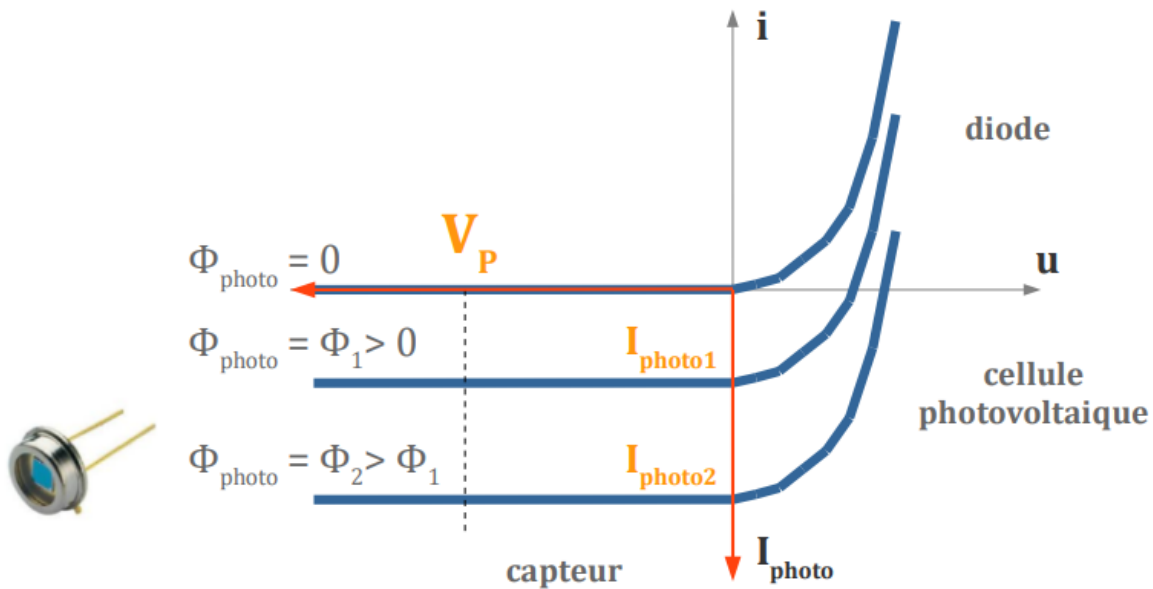
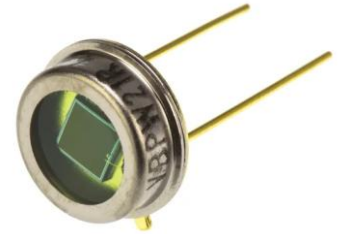
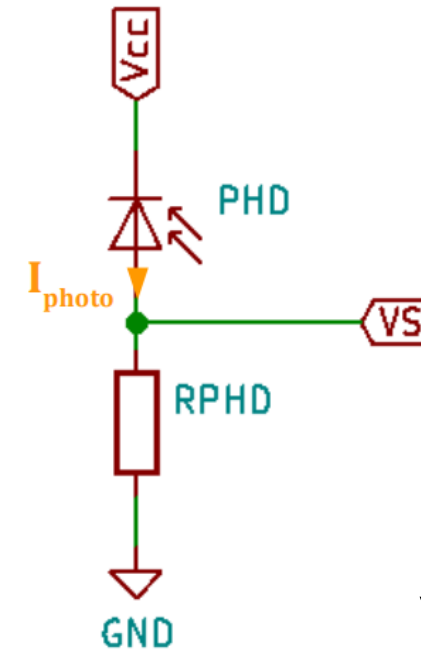


Diagram illustrating the formula for the photo-current I_{photo} as a function of the device area A , width W , and spectral sensitivity A/W :

$$I_{\text{photo}} = S_{\lambda} \cdot \eta \cdot \Phi_{\text{photo}}$$

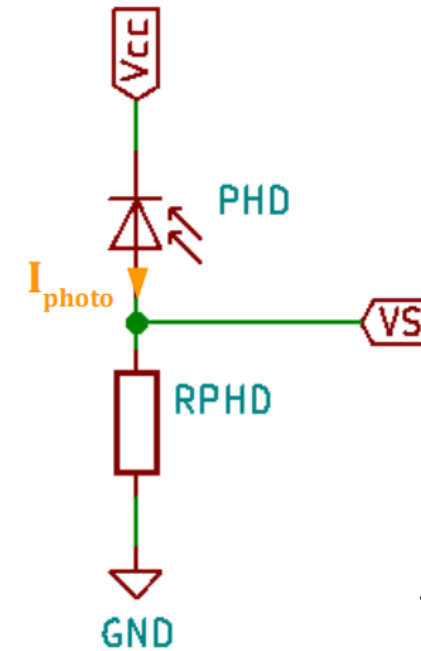
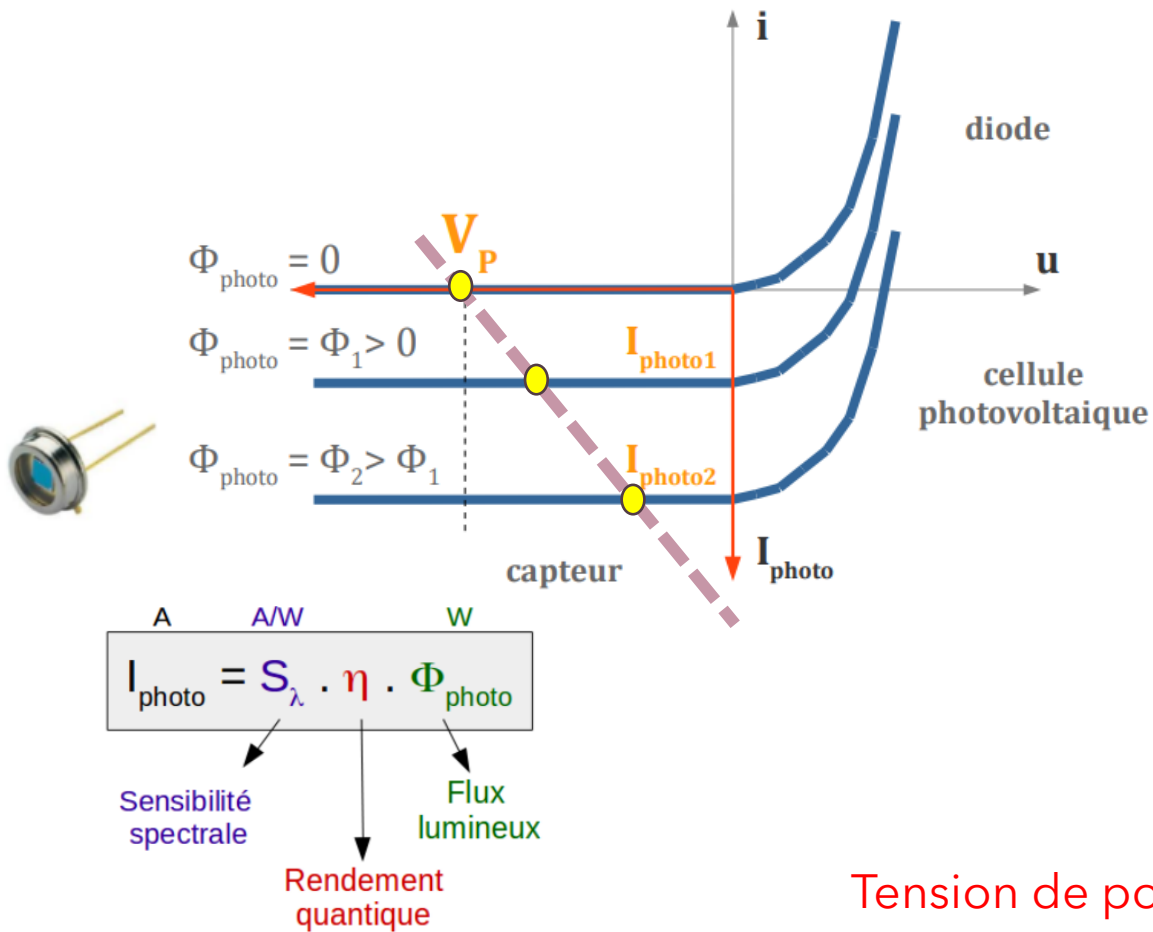
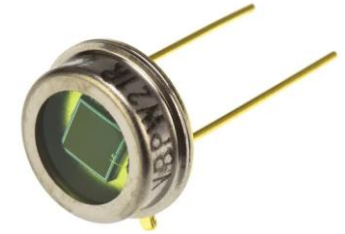
Where:

- S_{λ} : Sensibilité spectrale (Spectral sensitivity)
- η : Rendement quantique (Quantum efficiency)
- Φ_{photo} : Flux lumineux (Light flux)



$$V_S = R_{PHD} \cdot I_{\text{photo}}$$

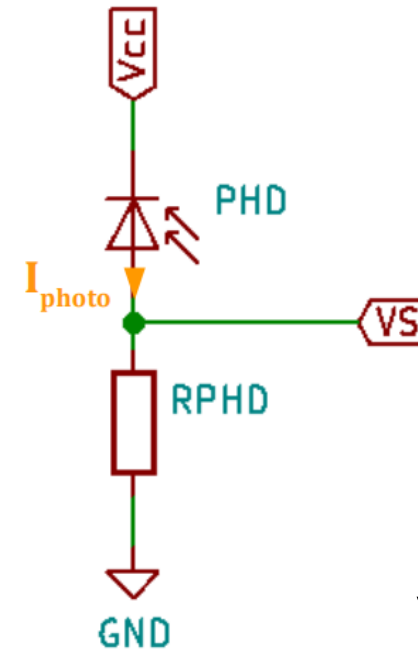
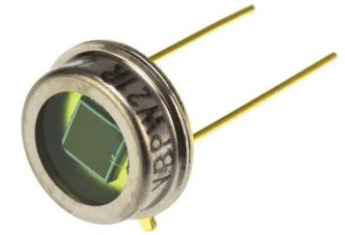
Montage de photodétection



$$V_S = R_{\text{PHD}} \cdot I_{\text{photo}}$$

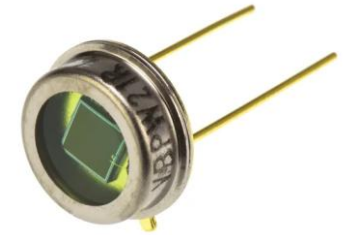
Tension de polarisation non constante

Etude expérimentale

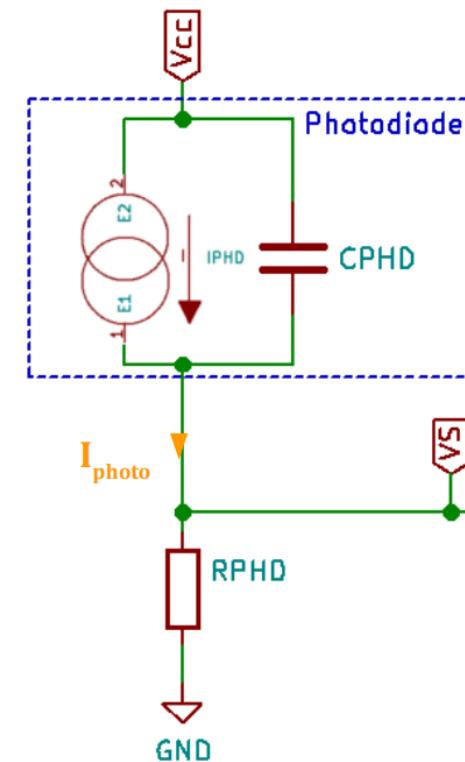


$$V_S = R_{PHD} \cdot I_{photo}$$

Modélisation



Bande passante réduite (à cause du système de mesure)



$$\frac{V_S}{I_{Phd}} = \frac{R_{eq}}{1 + j \cdot \omega \cdot R_{eq} \cdot C_{eq}}$$

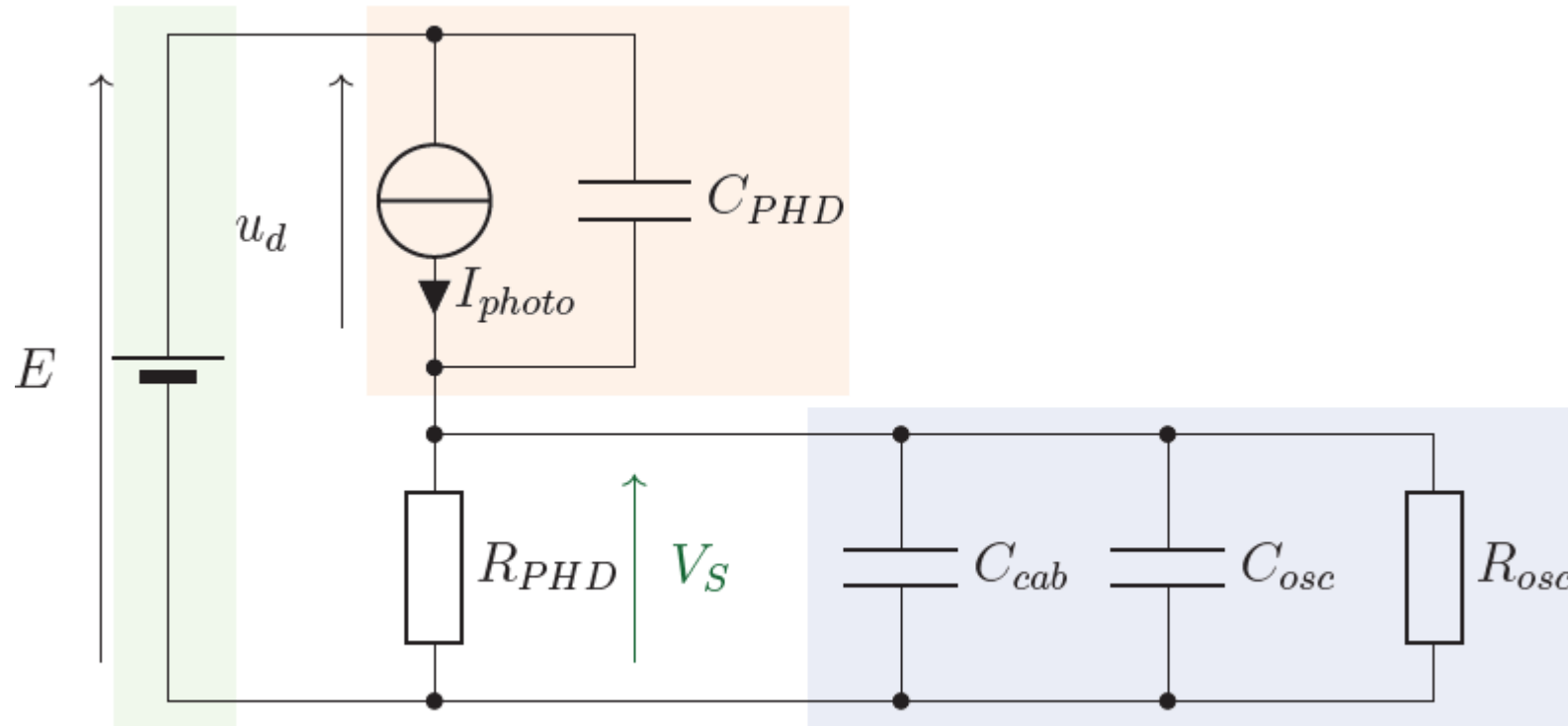
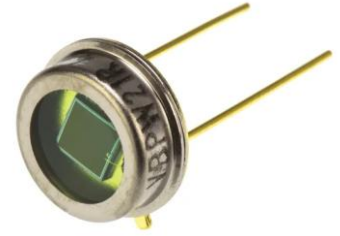
Avec :

$$R_{eq} = \frac{R_{phd} \cdot R_e}{R_{phd} + R_e}$$

$$C_{eq} = C_{phd} + C_e$$

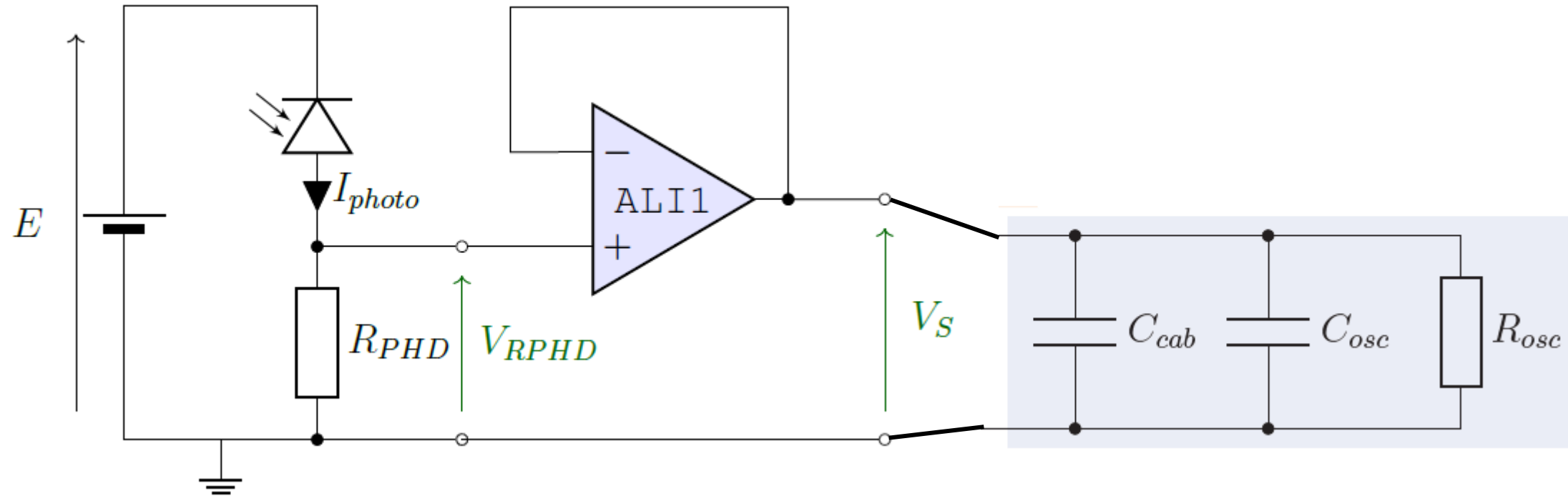
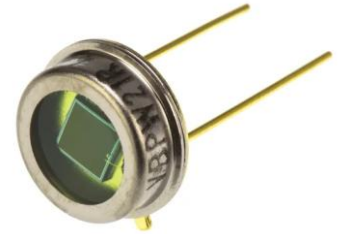
$$f_c = \frac{1}{2 \cdot \pi \cdot R_{eq} \cdot C_{eq}}$$

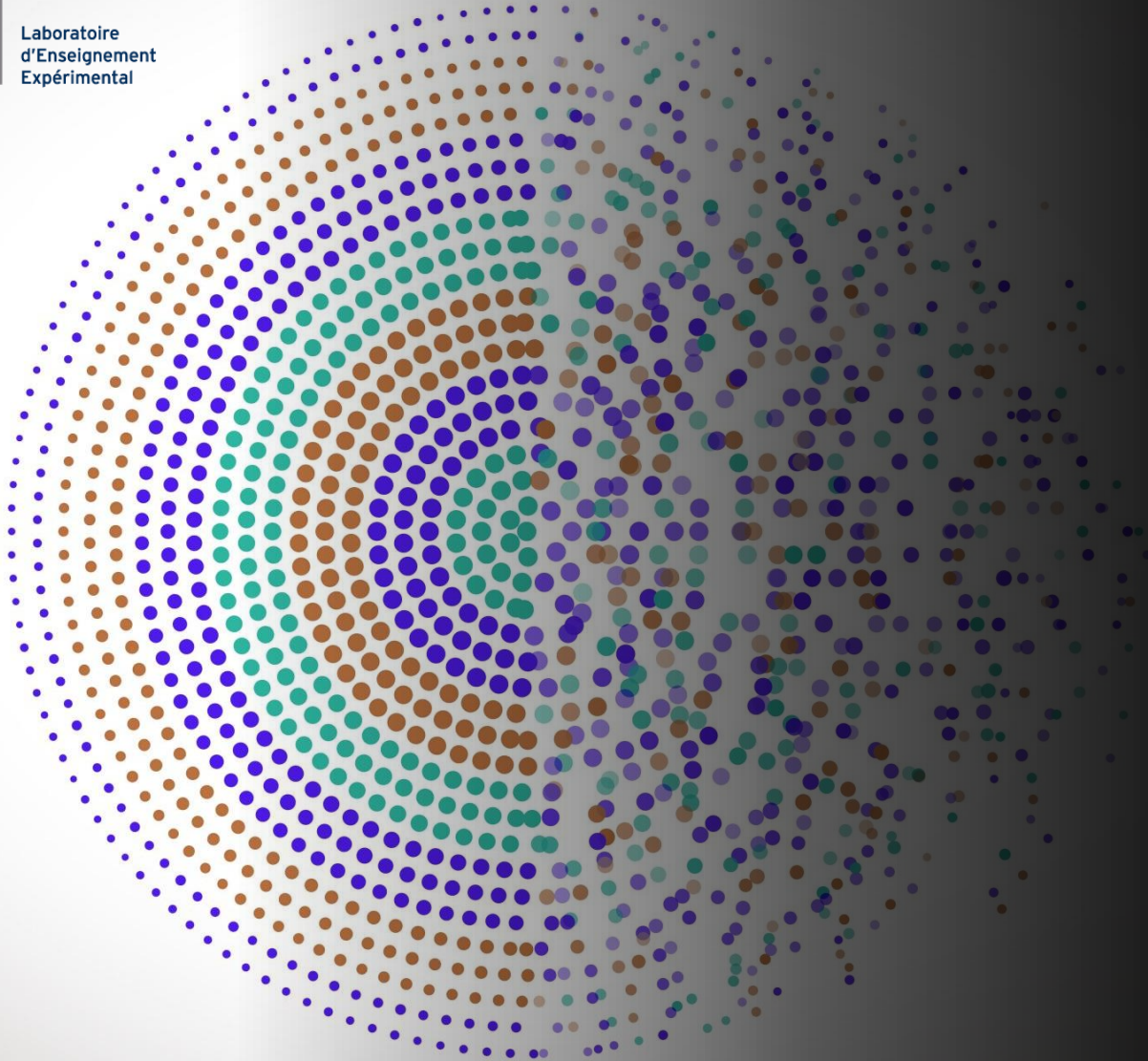
Modélisation



Bande passante réduite (à cause du système de mesure)

Amélioration / Montage Suiveur





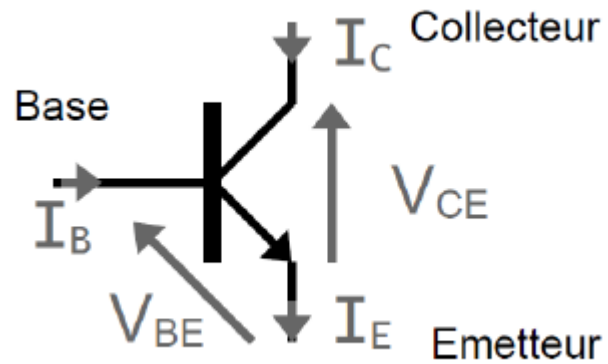
Transistor

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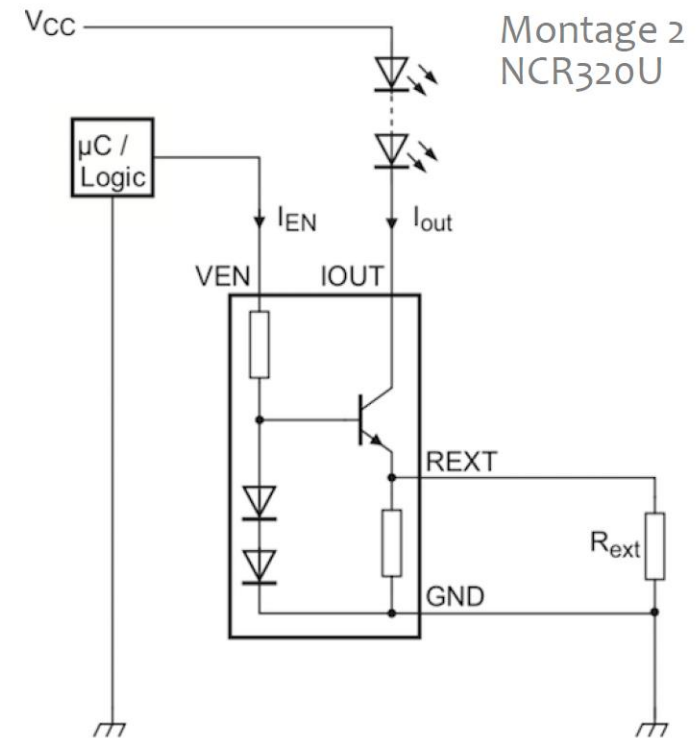
Transistor (bipolaire)

Adaptation de puissance



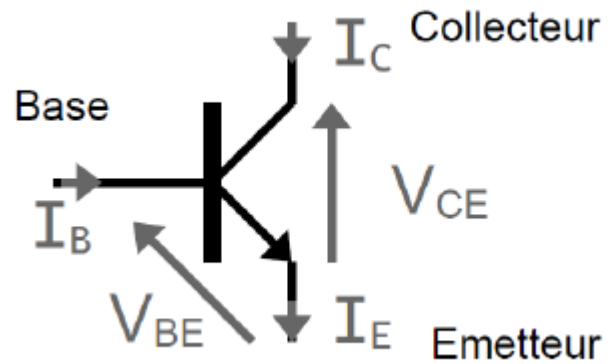
$$I_C = \beta \cdot I_B \quad \text{et} \quad I_E = I_C + I_B$$

$$I_C = \beta \cdot I_{BS} \cdot \exp(V_{BE}/U_T)$$



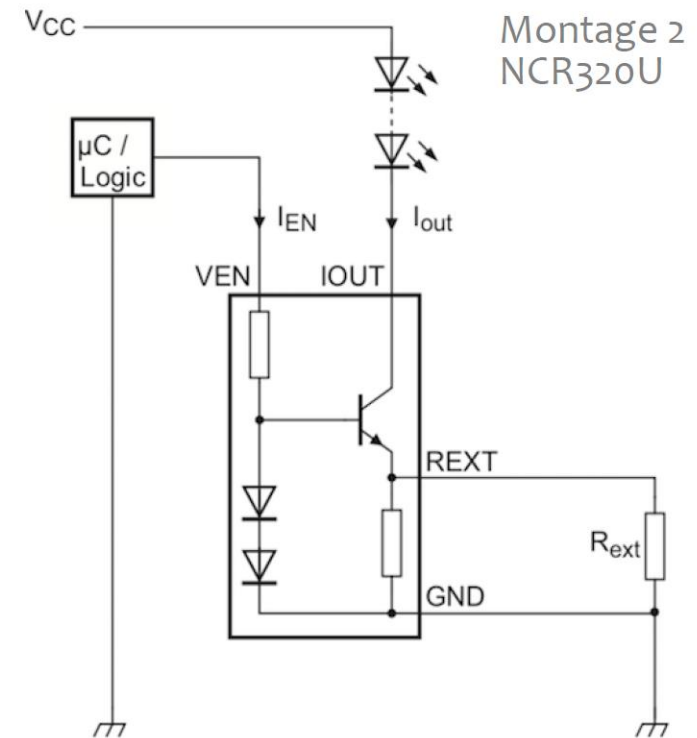
Transistor (bipolaire)

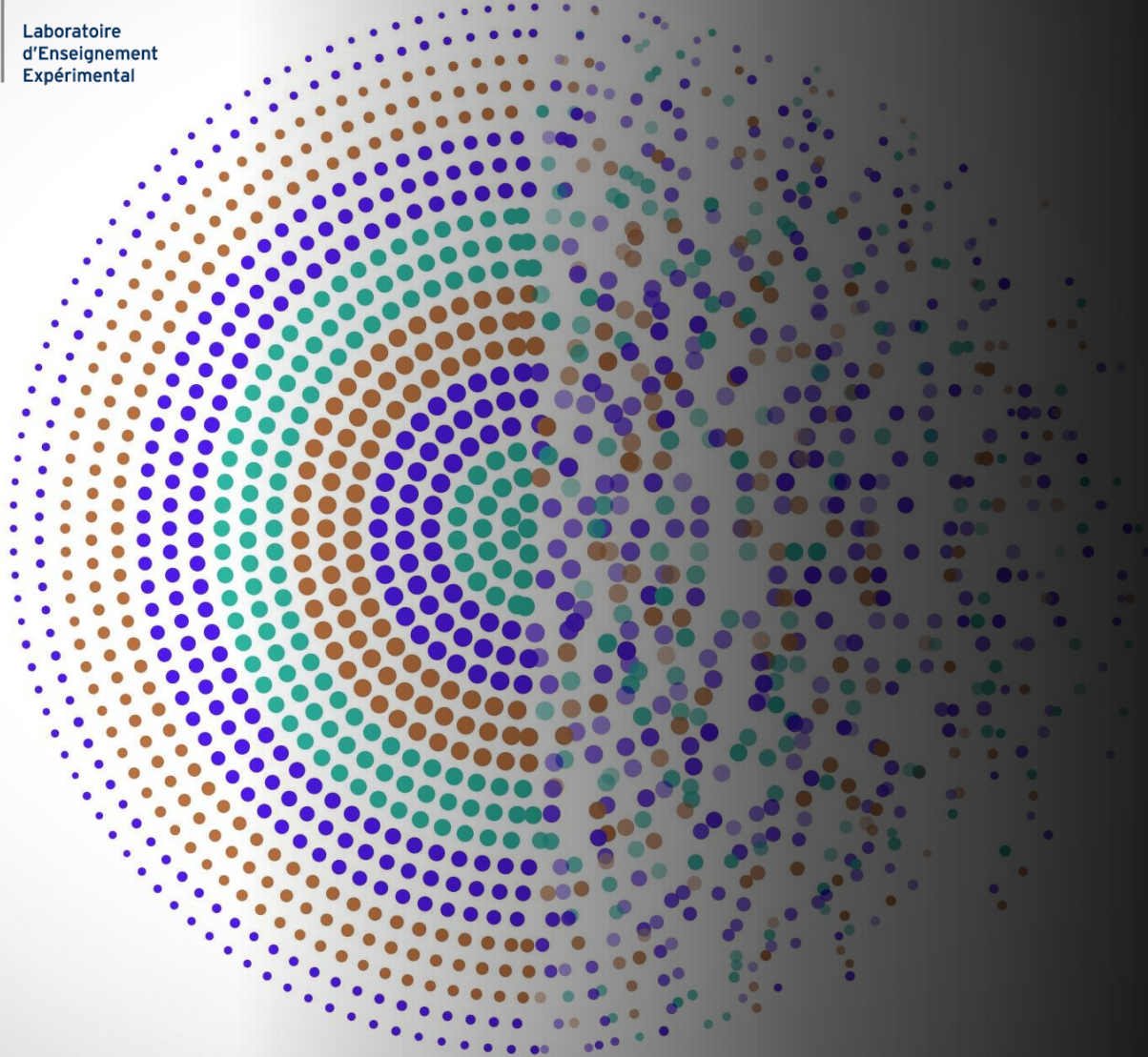
Adaptation de puissance



$$I_C = \beta \cdot I_B \quad \text{et} \quad I_E = I_C + I_B$$

$$I_C = \beta \cdot I_{BS} \cdot \exp(V_{BE}/U_T)$$





ALI / Amplificateur Linéaire Intégré

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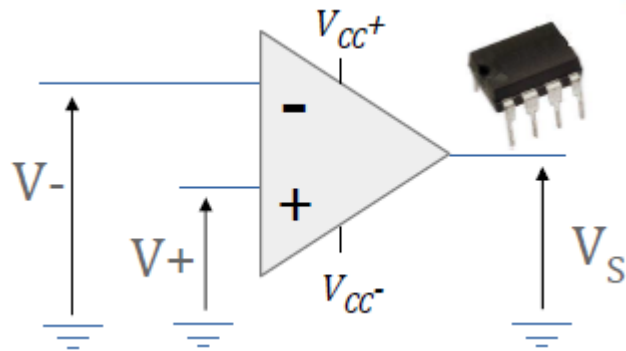
Amplificateur linéaire intégré / ALI

FONCTION DE TRANSFERT

$$V_S = A \cdot (V_+ - V_-)$$

avec $10^5 < A < 10^7$

Saturation à $V_S = V_{cc^+}$



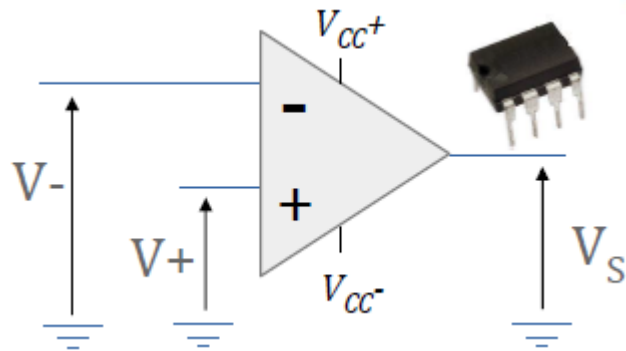
Amplificateur linéaire intégré / ALI

Fonctionnement boucle ouverte : comparateur

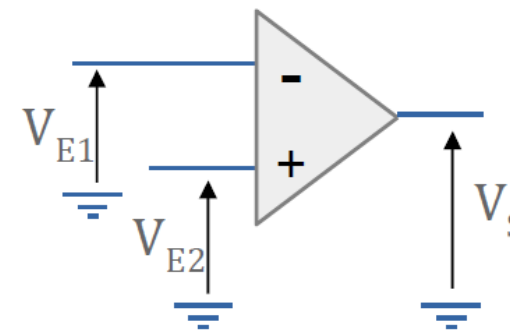
FONCTION DE TRANSFERT

$$V_S = A \cdot (V_+ - V_-)$$

avec $10^5 < A < 10^7$
Saturation à $V_S = V_{CC+}$



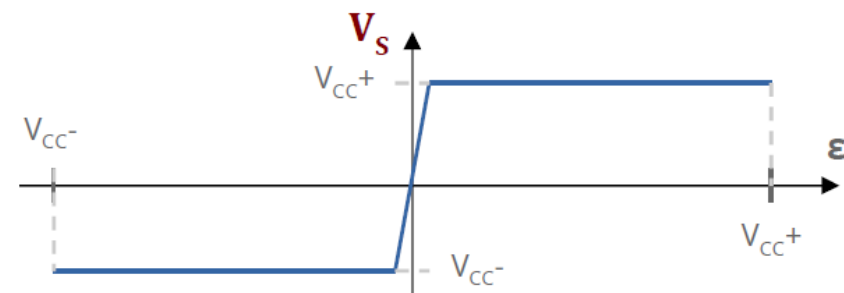
COMPARATEUR SIMPLE



$$V_S = V_{CC+} \quad \text{Si } V_{E2} > V_{E1}$$

$$V_S = V_{CC-} \quad \text{Si } V_{E1} > V_{E2}$$

Caractéristique $V_S = f(\epsilon)$ avec $\epsilon = V_+ - V_-$



Amplificateur linéaire intégré / ALI

Fonctionnement boucle ouverte : comparateur / Collecteur ouvert

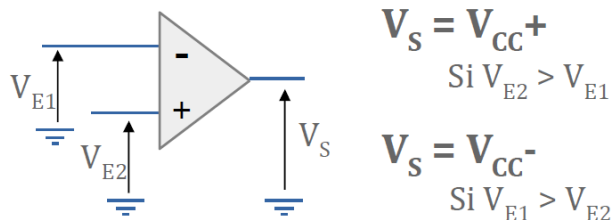
FONCTION DE TRANSFERT

$$V_S = A \cdot (V_+ - V_-)$$

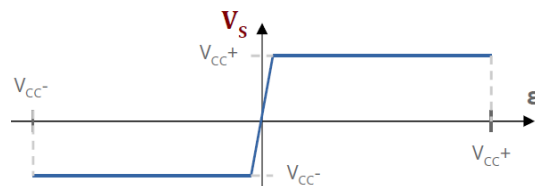
avec $10^5 < A < 10^7$

Saturation à $V_S = V_{CC+}$

COMPARATEUR SIMPLE



Caractéristique $V_S = f(\epsilon)$ avec $\epsilon = V_+ - V_-$



COLLECTEUR OUVERT / ÉMETTEUR OUVERT

Comparateur associé à un transistor

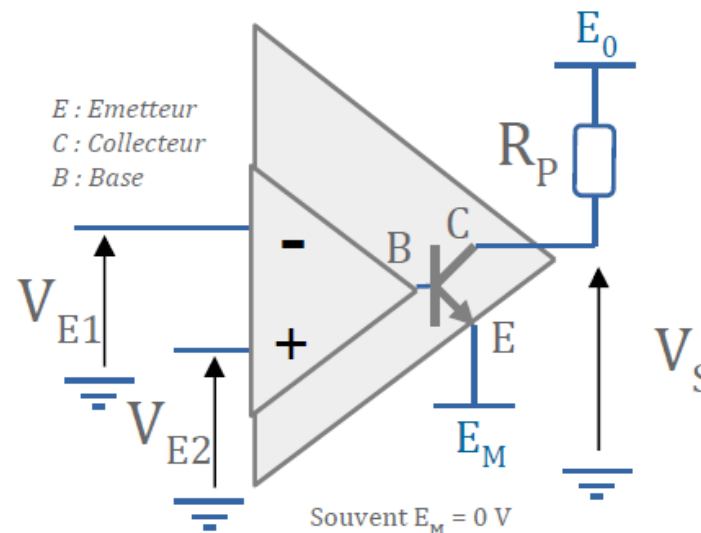
T :

I_B : courant entrant dans la base

I_C : courant entrant dans le collecteur

→ si $I_B > 0$ alors $I_C > 0$, T = interrupteur fermé

→ sinon $I_C = 0$, T = interrupteur ouvert



Si $V_{E2} > V_{E1}$
→ $I_B > 0$

$$V_S = E_M$$

Si $V_{E1} > V_{E2}$
→ $I_B = 0$

$$V_S = E_0$$

Amplificateur linéaire intégré / ALI

Fonctionnement boucle fermée : mode linéaire

FONCTION DE TRANSFERT

$$V_S = A \cdot (V_+ - V_-)$$

avec $10^5 < A < 10^7$
Saturation à $V_S = V_{cc+}$

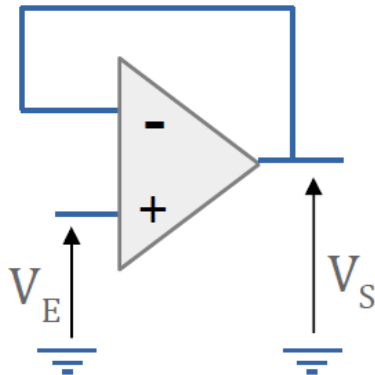
Si contre-réaction négative (via un dipôle)

► REGIME LINEAIRE

► $V_+ = V_-$

Hypothèse à vérifier...

SUIVEUR



$$V_S = V_E$$

Adaptation
d'impédance

Amplificateur linéaire intégré / ALI

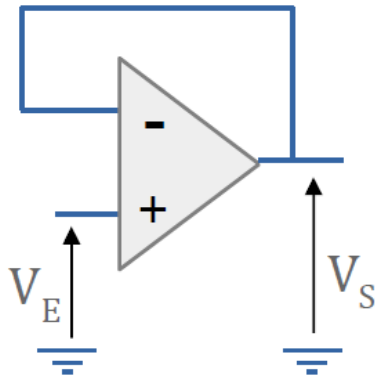
Fonctionnement boucle fermée : mode linéaire

FONCTION DE TRANSFERT

$$V_S = A \cdot (V_+ - V_-)$$

avec $10^5 < A < 10^7$
Saturation à $V_S = V_{cc+}$

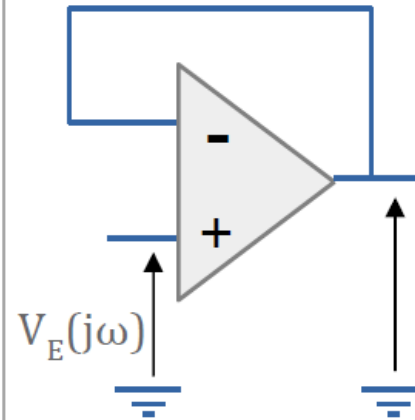
SUIVEUR



$$V_S = V_E$$

Adaptation
d'impédance

FONCTION DE TRANSFERT EN SUIVEUR



A partir de l'équation ci-contre,
on obtient pour ce circuit (suiveur) :

$$V_S(j\omega) = A(j\omega) \cdot [V_E(j\omega) - V_S(j\omega)]$$

On obtient la fonction de transfert suivante :

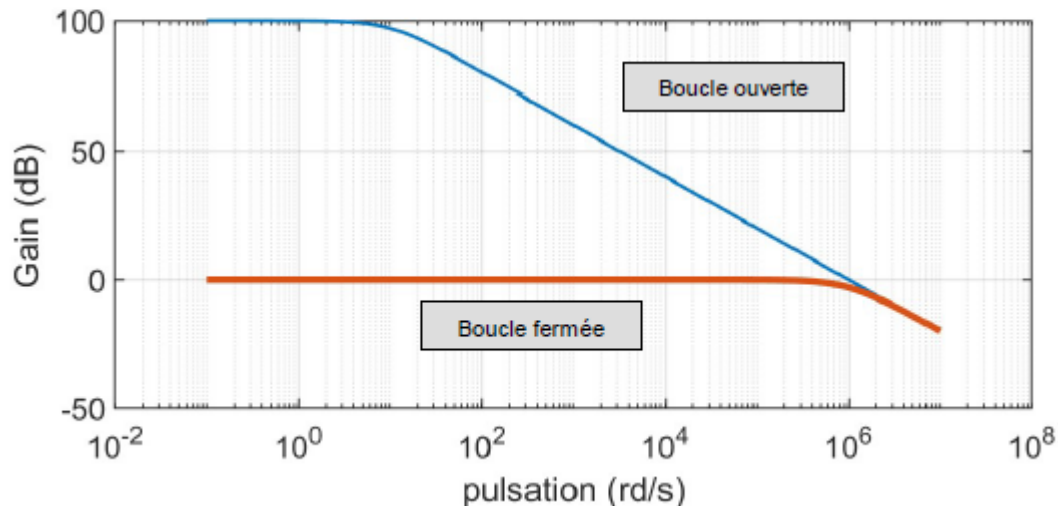
$$T(j\omega) = \frac{V_S(j\omega)}{V_E(j\omega)} = \frac{A(j\omega)}{1 + A(j\omega)}$$

Amplificateur linéaire intégré / ALI

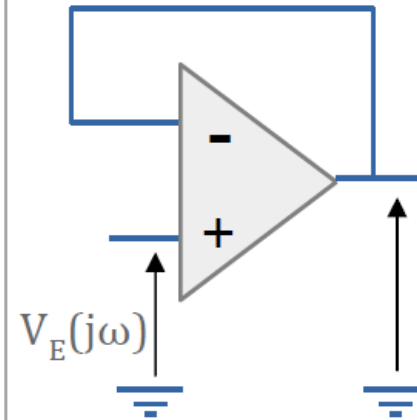
Fonctionnement boucle fermée : mode linéaire

RÉPONSE EN FRÉQUENCE

Exemple d'un ALI ayant un produit gain – bande-passante $GBW = 1 \text{ MHz}$ et une amplification différentielle de 10^5 (identique ci-contre) et le rebouclage en mode suiveur.



FONCTION DE TRANSFERT EN SUIVEUR



A partir de l'équation ci-contre, on obtient pour ce circuit (suiveur) :

$$V_S(j\omega) = A(j\omega) \cdot [V_E(j\omega) - V_S(j\omega)]$$

On obtient la fonction de transfert suivante :

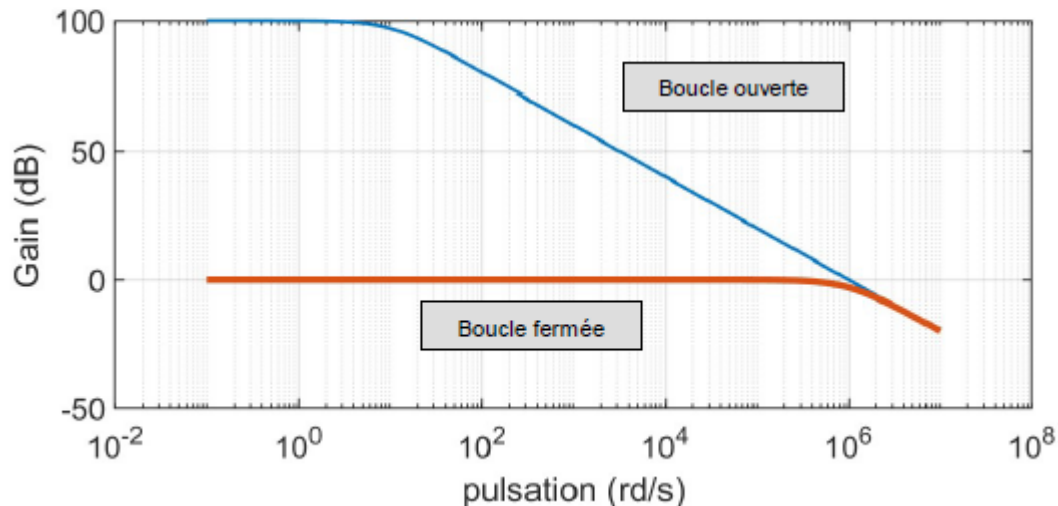
$$T(j\omega) = \frac{V_S(j\omega)}{V_E(j\omega)} = \frac{A(j\omega)}{1 + A(j\omega)}$$

Amplificateur linéaire intégré / ALI

Fonctionnement boucle fermée : mode linéaire

RÉPONSE EN FRÉQUENCE

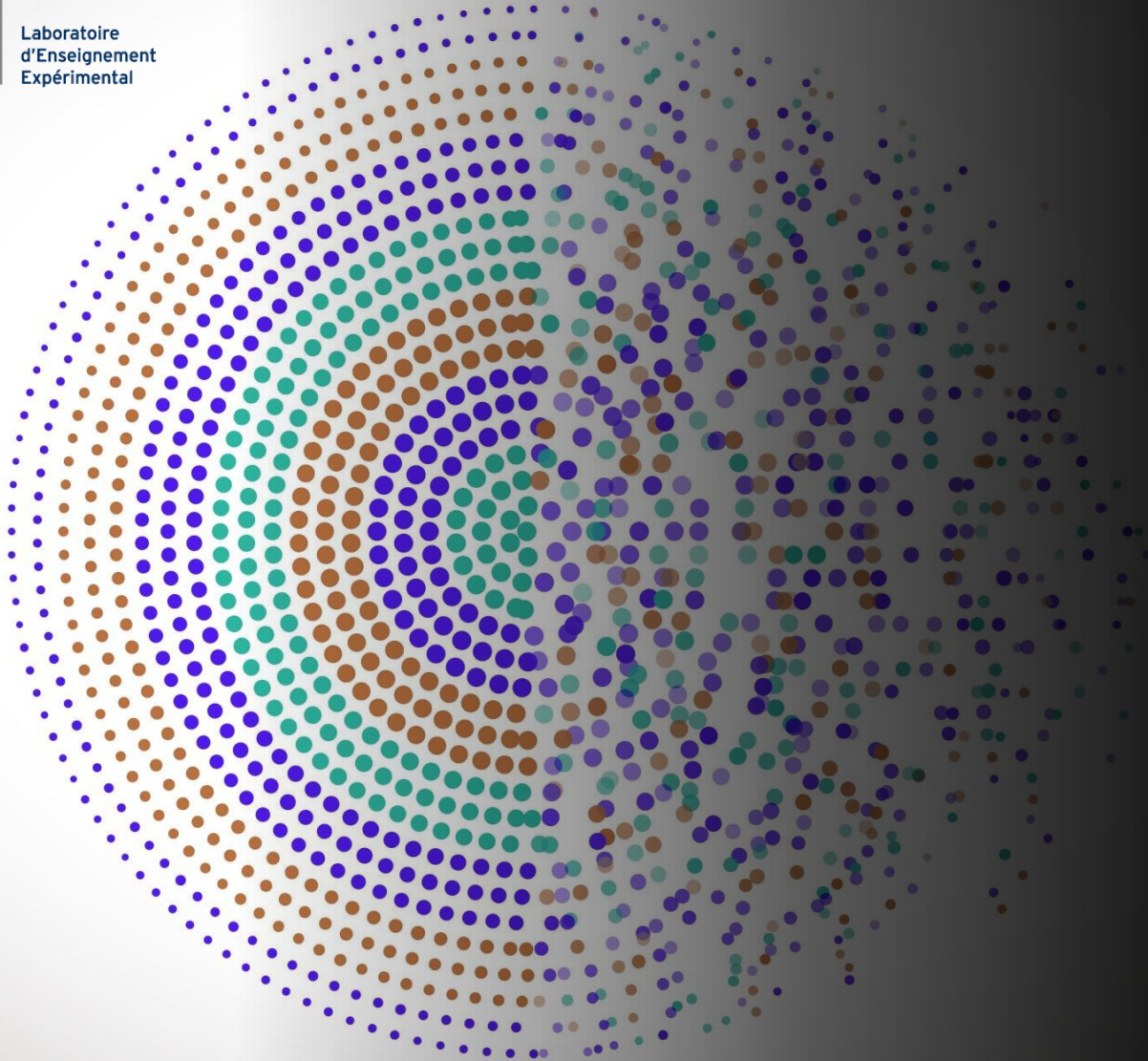
Exemple d'un ALI ayant un produit gain – bande-passante $GBW = 1 \text{ MHz}$ et une amplification différentielle de 10^5 (identique ci-contre) et le rebouclage en mode suiveur.



Propriété des montages à ALI

► $A.BP = \text{cte}$

Où A est l'amplification du montage
BP la bande passante du montage



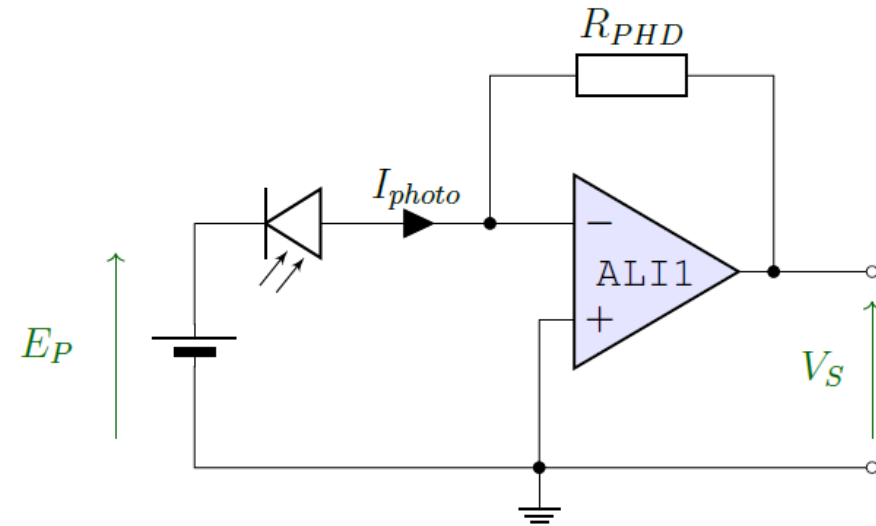
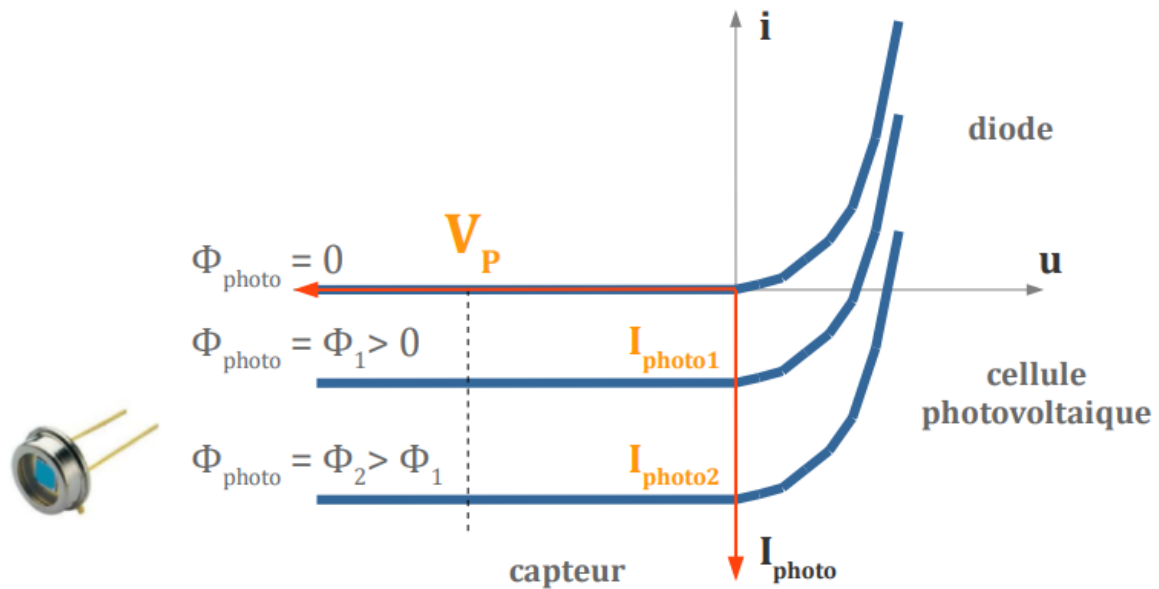
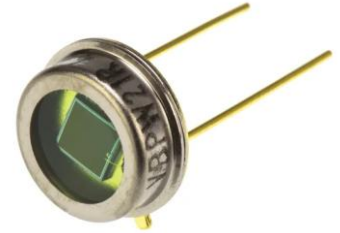
Photodétection

Montage transimpédance

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Montage transimpédance

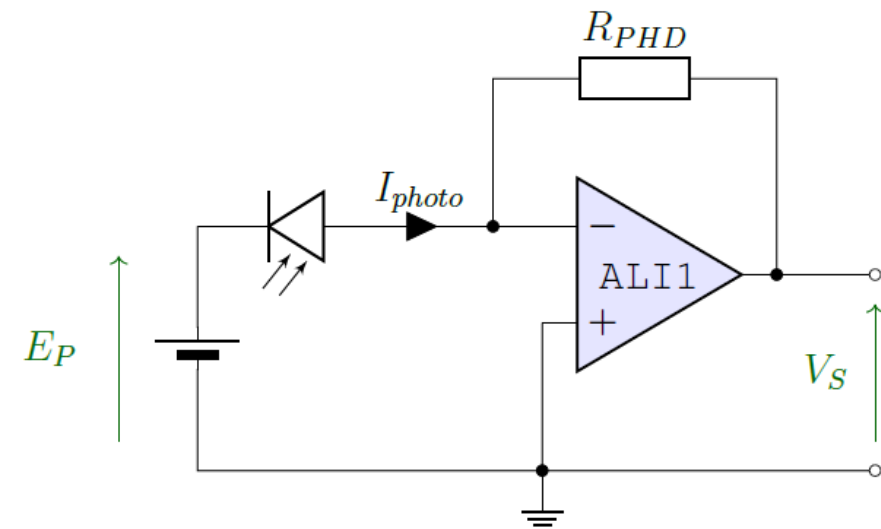
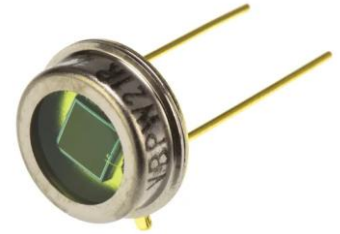


$$I_{photo} = S_{\lambda} \cdot \eta \cdot \Phi_{photo}$$

S_{λ} : Sensibilité spectrale
 η : Rendement quantique
 Φ_{photo} : Flux lumineux

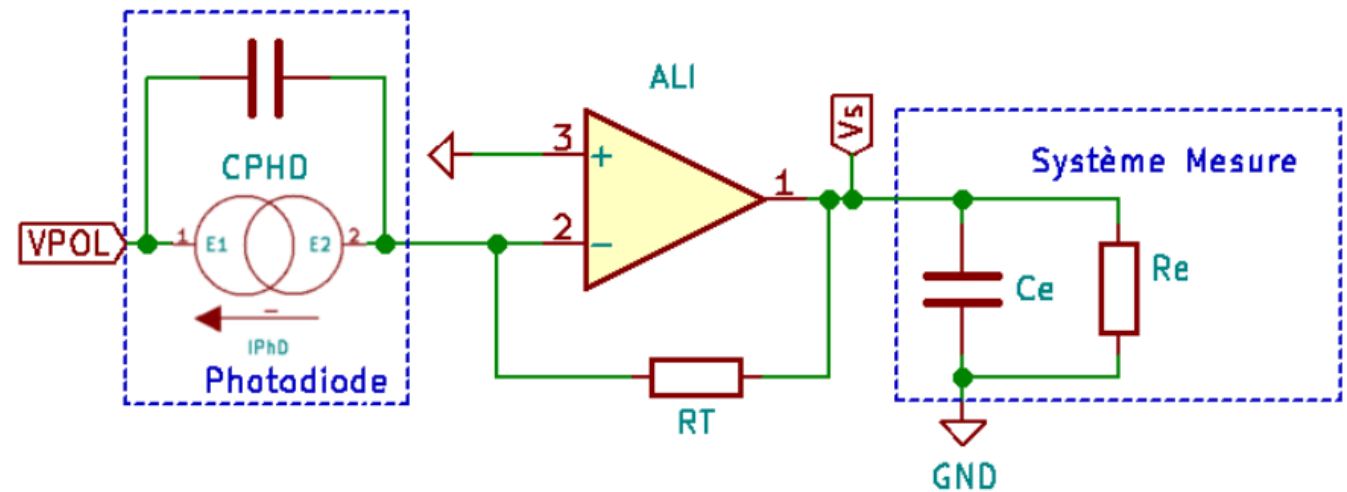
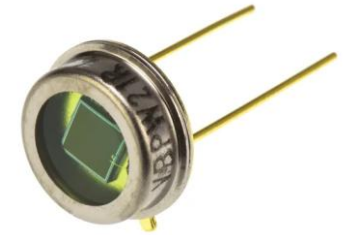
$$V_S = - R_{PHD} \cdot I_{photo}$$

Etude expérimentale



$$V_S = - R_{PhD} \cdot I_{photo}$$

Modélisation



ALI / Passe-bas

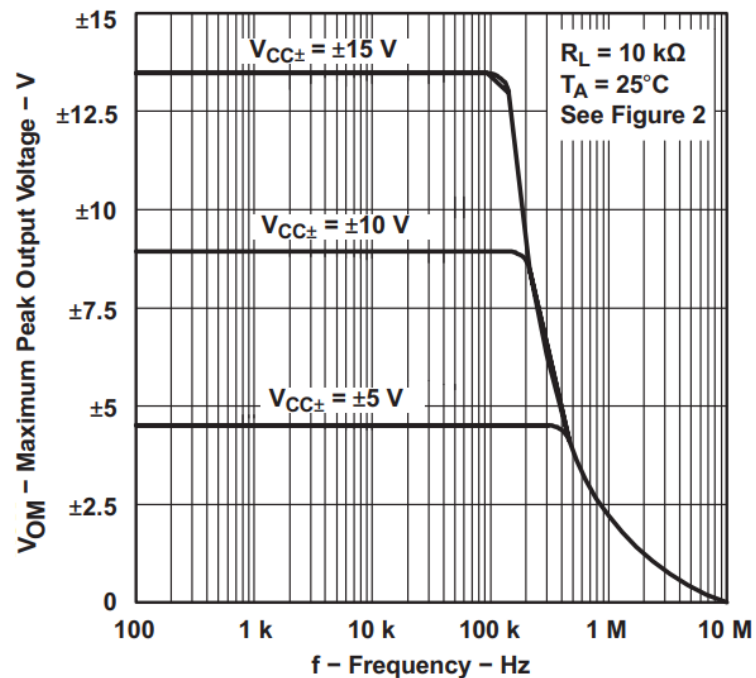


Figure 6-41. Maximum Peak Output Voltage vs Frequency

Produit Gain-Bande-Passante constant

INPUT CAPACITANCE				
Z_{ID}	Differential		100 \parallel 2	M Ω \parallel pF
Z_{ICM}	Common-mode		6 \parallel 1	T Ω \parallel pF
OPEN-LOOP GAIN				
A_{OL}	Open-loop voltage gain	$V_S = 40$ V, $V_{CM} = V_S / 2$, (V_{CC-}) + 0.3 V < V_O < (V_{CC+}) - 0.3 V	118 125	dB
A_{OL}	Open-loop voltage gain	$V_S = 40$ V, $V_{CM} = V_S / 2$, $R_L = 2$ k Ω , (V_{CC-}) + 1.2 V < V_O < (V_{CC+}) - 1.2 V	115 120	dB
FREQUENCY RESPONSE				
GBW	Gain-bandwidth product		5.25	MHz
SR	Slew rate	$V_S = 40$ V, $G = +1$, $C_L = 20$ pF	20	V/ μ s

ALI asservi / Modélisation

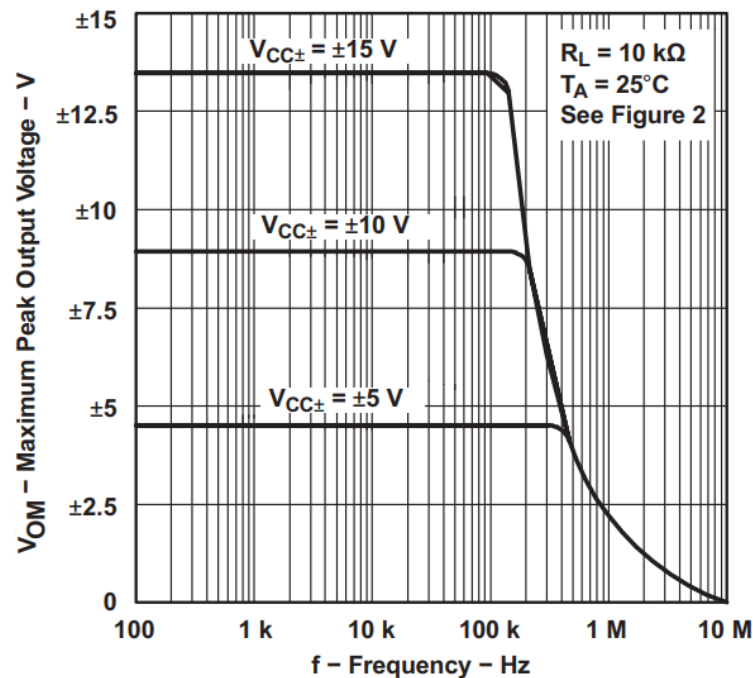
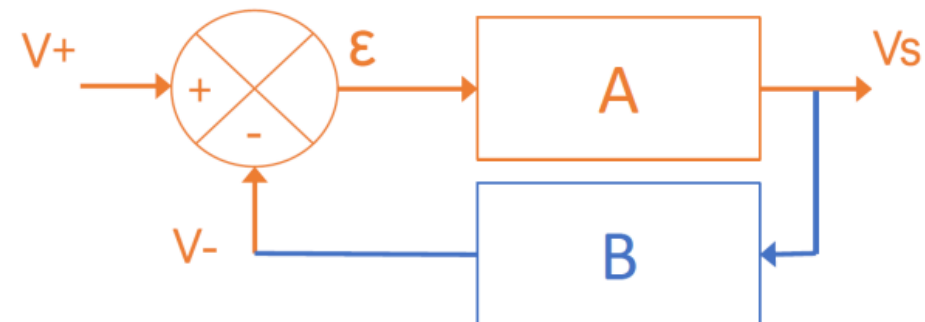


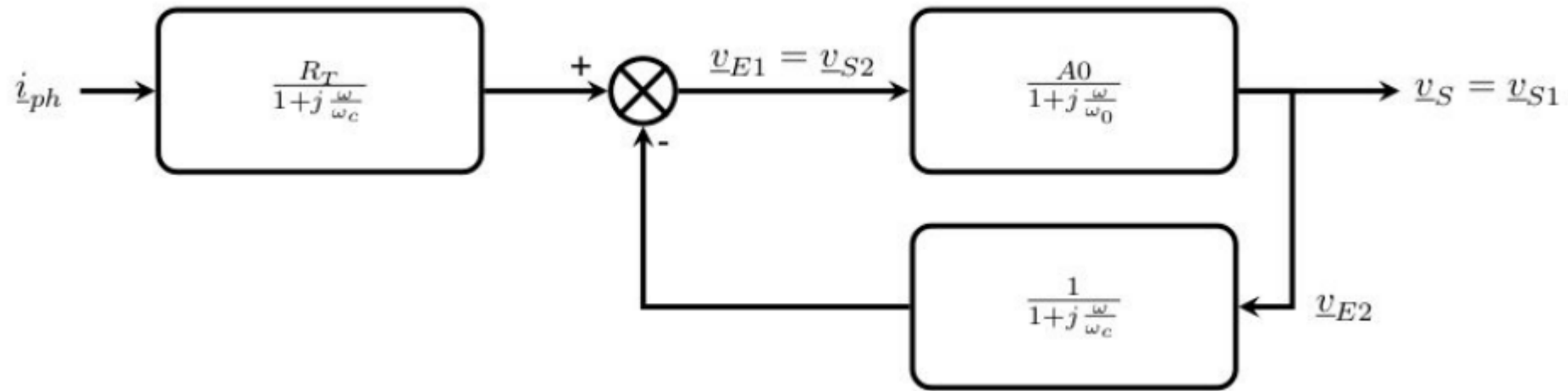
Figure 6-41. Maximum Peak Output Voltage vs Frequency

$$A(j\omega) = \frac{A_{MAX}}{1 + j \frac{\omega}{\omega_c}}$$



$$V_s = \frac{A(j\omega)}{1 + A(j\omega) \cdot B(j\omega)} V_E$$

Transimpédance / Modélisation



$$\frac{V_S}{I_{Phd}} = \frac{R_T \cdot A_0}{\left(1 + \frac{j \cdot \omega}{\omega_0}\right) \cdot \left(1 + \frac{j \cdot \omega}{\omega_c}\right) + A_0}$$

$$V_S = \frac{A(j\omega)}{1 + A(j\omega) \cdot B(j\omega)} V_E$$